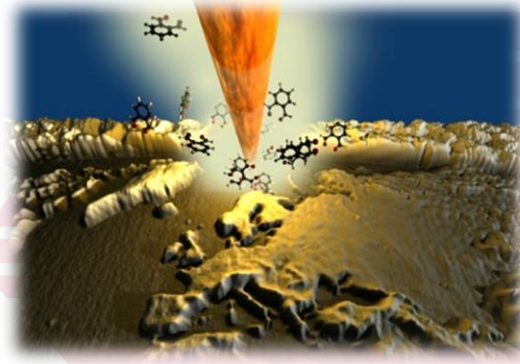


热式扫描探针纳米加工技术



柳 洋 187 0136 3677

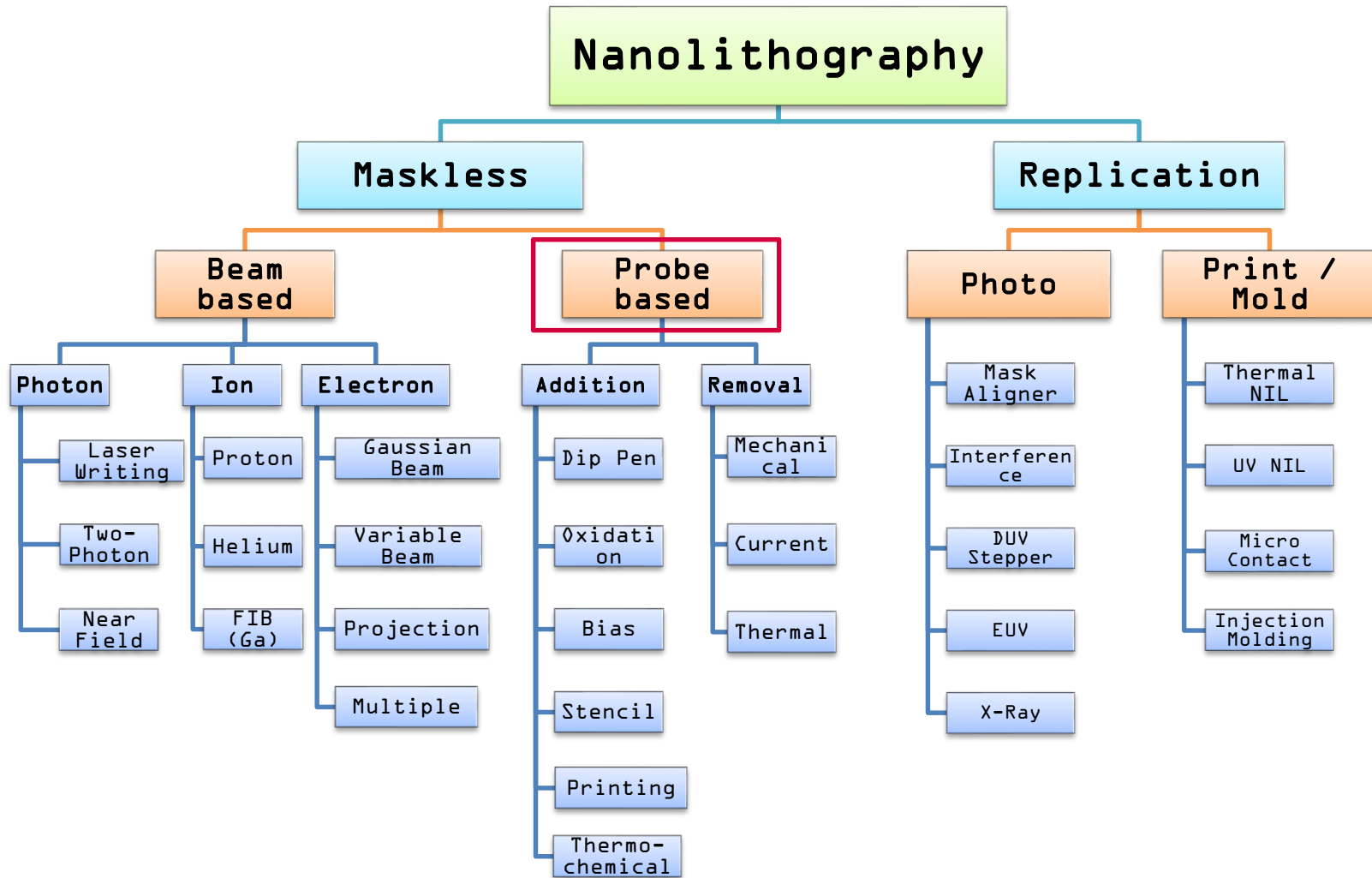
Quantum Design 中国子公司

2017.07.11

主要内容

- 微纳加工技术简介
- 热式扫描探针技术
- 应用领域及案例
- 总结

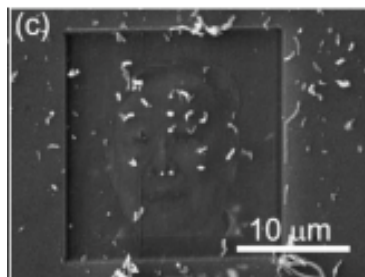
微纳米加工技术简介



微纳米加工技术简介

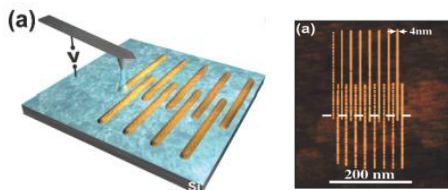
扫描探针图形直写技术 (SPL)

纳米雕刻 Nano-Scratching



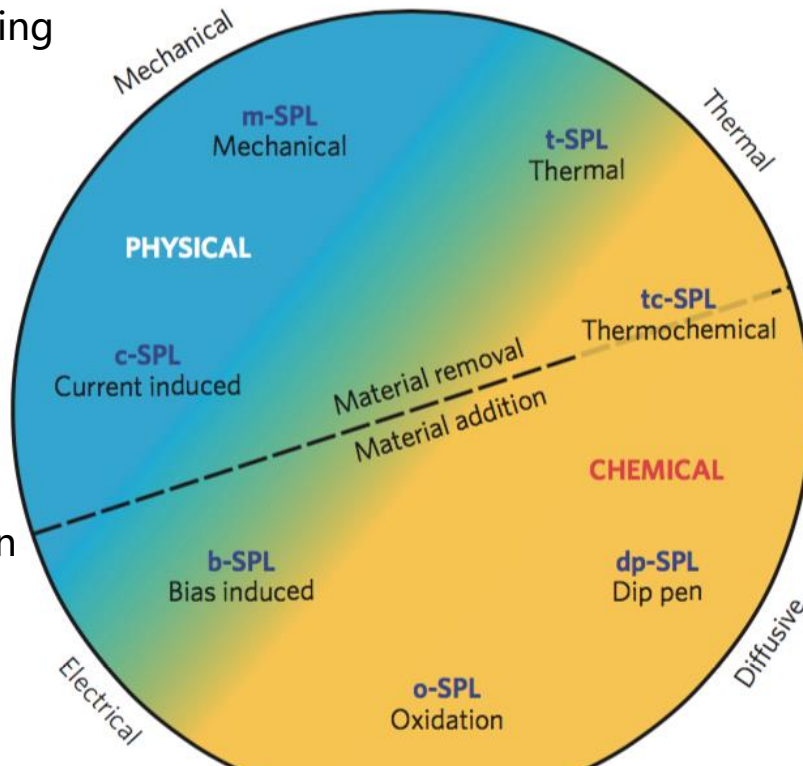
Dong et al., small, 2010

电场诱导沉积
Field-induced deposition

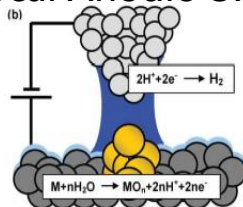


Garcia et al., Nano Lett. 2007, 7, 1846.

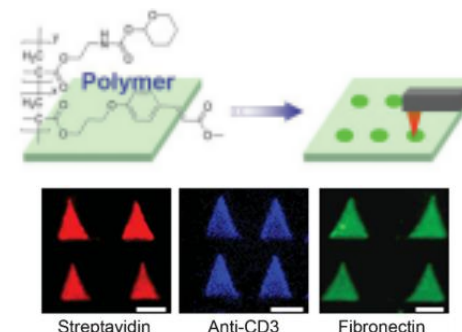
Advanced Scanning Probe Lithography
Nature Nanotechnology, 9, 577-587, (2014)



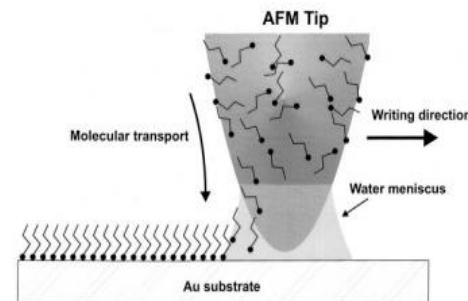
Local Anodic Oxidation



热化学 Thermochemical



纳米蘸印 Dip-Pen



Mirkin et al., Science 1999, 283, p661

热式扫描探针技术介绍

Origins

STM + AFM

1986

IBM Research Zurich

Stanford

Dr. Binnig & Rohrer



Nobelprize 1986

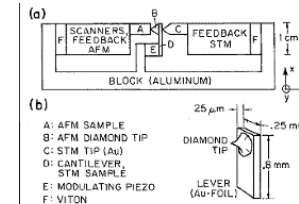


FIG. 2. Experimental setup. The lever is not to scale in (a). Its dimensions are given in (b). The STM and AFM piezoelectric drives are facing each other, sandwiching the diamond tip that is glued to the lever.

First AFM (Binnig, Quate, Gerber)

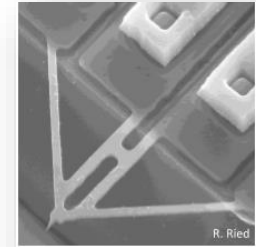
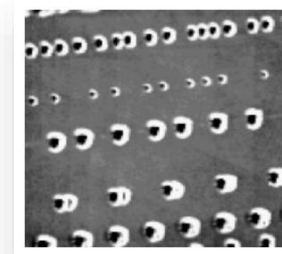
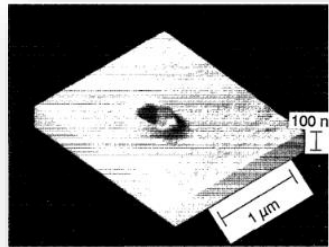
1st heated AFM tips

1992 – 1999

IBM Research Almaden

Stanford

Rugar, Mamin



Data storage with heated AFM tips

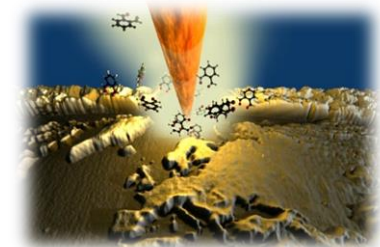
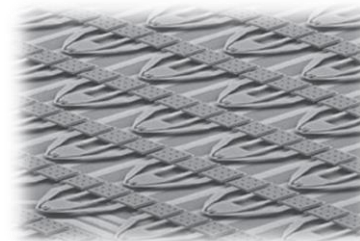
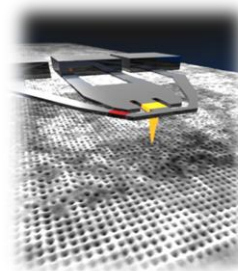
Millipede 基于探针

高密度存储技术

1995 – 2007

IBM Research Zurich

Vettiger, Binnig



热式扫描探针技术介绍

瑞士 Swisslitho AG 公司

Spinoff 

- ◆ 2012: 由Felix Holzner 和 Philip Paul建立
- ◆ IBM Millipede基于探针技术的高密度存储项目衍生技术，用于纳米结构制备
- ◆ 主页: www.swisslitho.com



Origin of
technology:



Zurich



Zurich Technopark

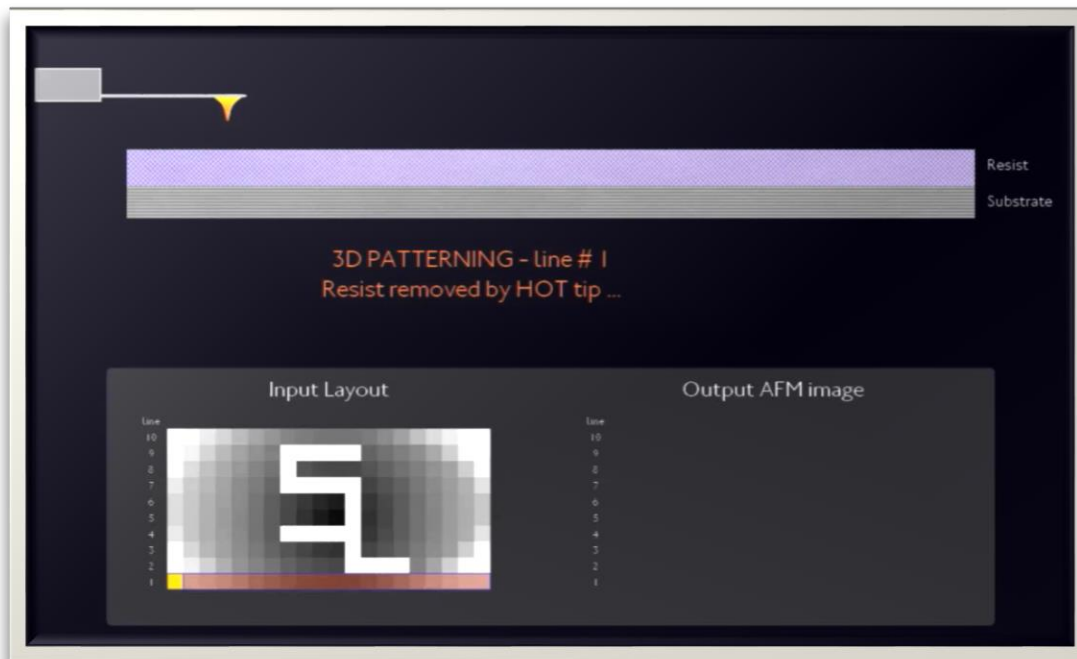


热式扫描探针技术介绍

工作原理

优势：

- ◆ “所见即所得”
- ◆ 省去测量验证步骤
- ◆ 增加可靠性

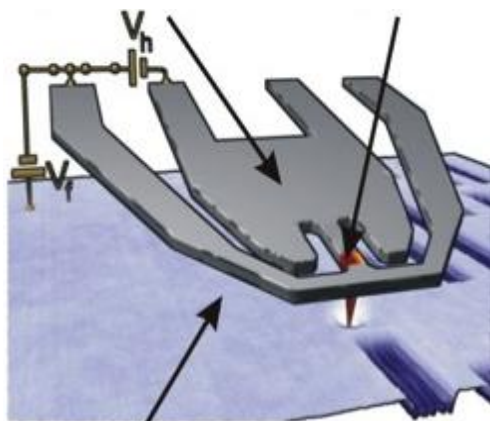


- ◆ **PPA(聚苯二醛) 直写胶涂敷**在样品表面。
- ◆ **背热式直写探针**，针尖温度可达300~400°C。与针尖接触的PPA受热瞬间分解，周围部分由于PPA热导率低而不受影响。
- ◆ **热针震动模式直写**，直写时探针加热，每次下针幅度受静电力控制，垂直精度1nm，从而写出3D图形。
- ◆ **冷针接触模式扫描**，回程扫描时探针冷却，由侧壁的热感应器探测样品高度变化(精度0.1nm)，获得样品形貌。回路数据修正下一行直写。

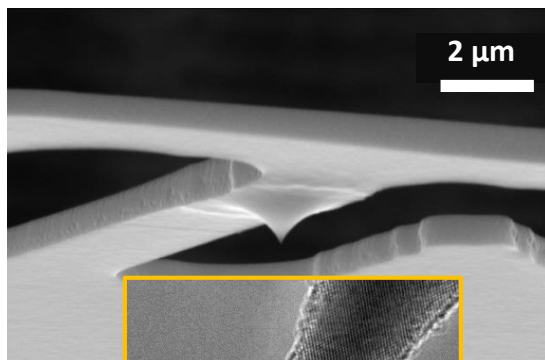
热式扫描探针技术介绍

静电力驱动

针尖加热



热学表面形貌传感器



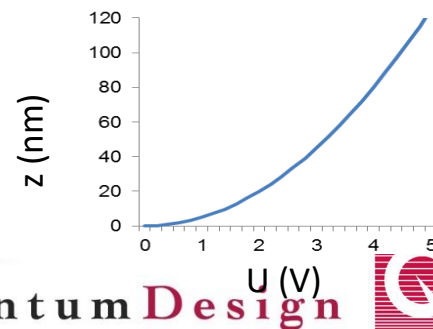
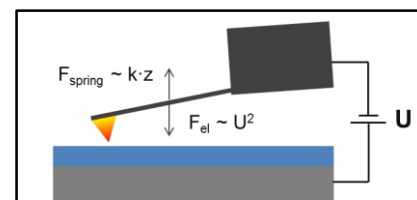
发光点为针尖加热点
($T = 1000^{\circ}\text{C}$)

t-SPL直写针尖

主要特点

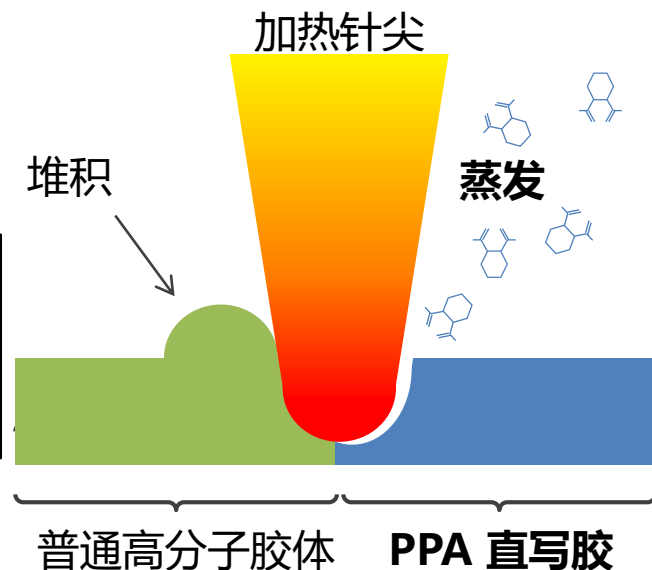
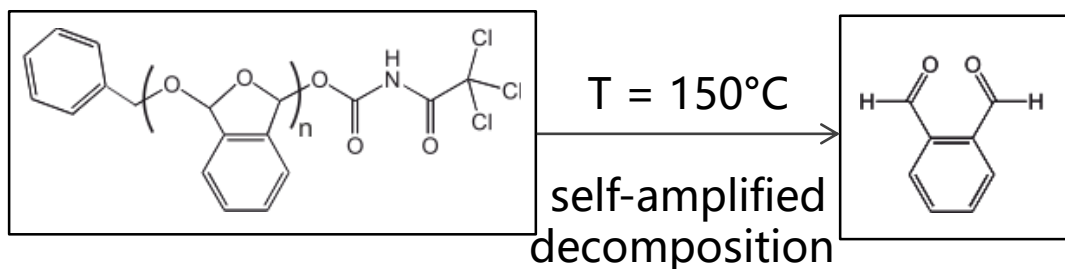
- ▶ 高锐度针尖 \Rightarrow 5 nm 直径
- ▶ 电阻式针尖加热 \Rightarrow 高达 400°C
- ▶ 形貌传感器 \Rightarrow ~ 0.1 nm 敏感度
- ▶ 静电力激发 \Rightarrow 下探时间 $< 1 \mu\text{s}$
1 nm 准确度

静电力驱动



直写胶技术

高分子链分解



PPA (polyphthalaldehyde聚苯二醛)

- ▶ 吸热分解为易蒸发单体
- ▶ 可通过匀胶工艺涂覆

Coulebrier *et al.*, *Macromolecules*, (2010)

需具备的性质:

- ▶ 有效的热激发工艺
- ▶ 图形转移的稳定性
- ▶ 可靠，易操作

热式扫描探针技术介绍



For Scientist , By Scientist

2014

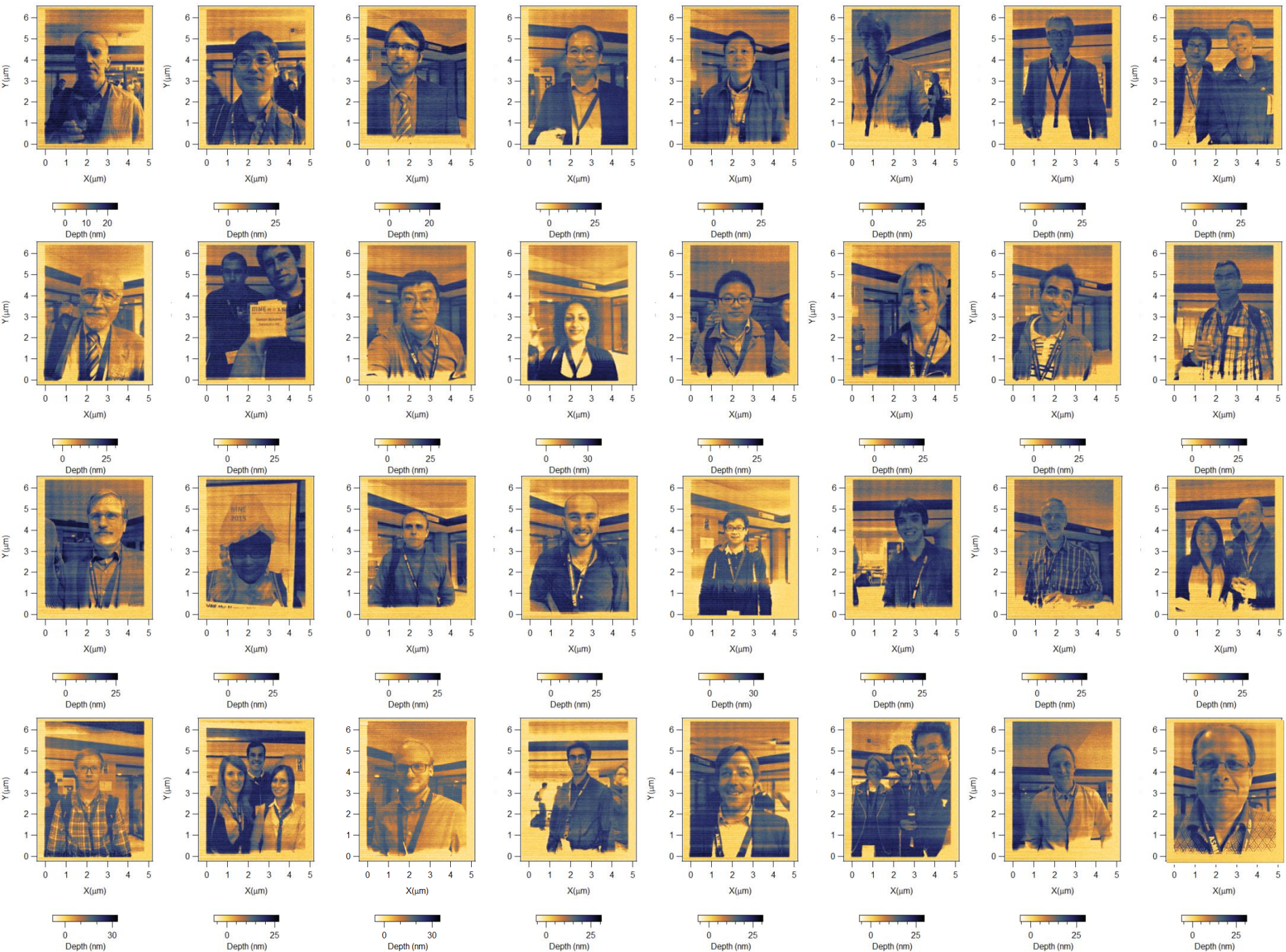


MNE 2014 in Lausanne:

≈ 100 余人现场直写

Quantum Design





热式扫描探针技术介绍

技术特点：

- ◆ 3D纳米直写能力
高直写精度 (XY: 10nm, Z: 1nm)
高速直写 20 mm/s 与EBL媲美
- ◆ 无需显影，实时观察直写效果
形貌感知灵敏度0.1nm
样品无需标记识别，多结构套刻，对准精度 5nm
- ◆ 无临近效应
- ◆ 无电子/离子损伤
- ◆ 区域热加工和改性
- ◆ 大面积直写 100mmX100mm

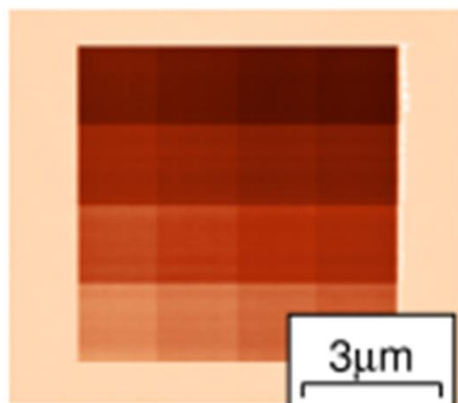
NanoFrazor- explore



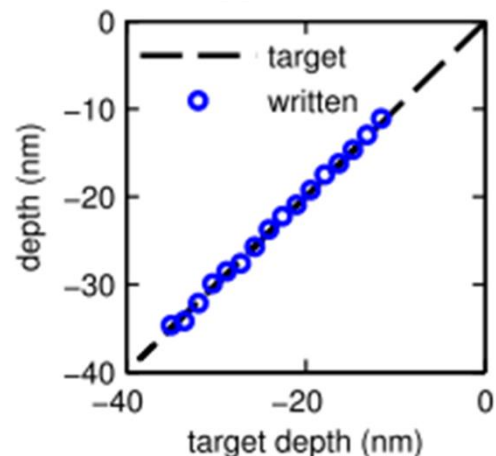
热式扫描探针技术介绍

3D 纳米结构直写

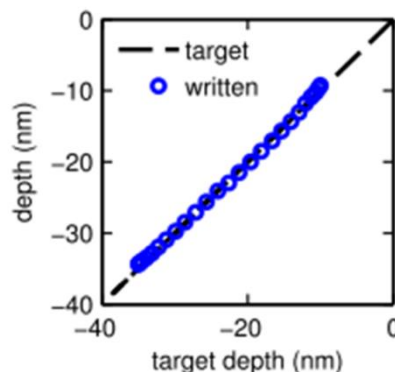
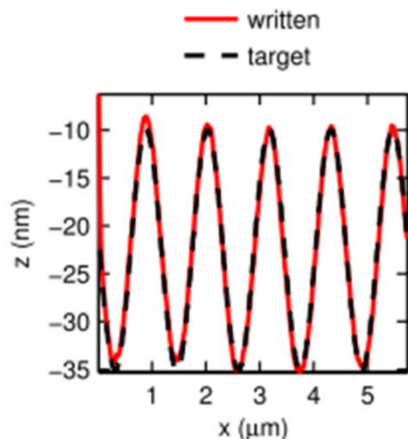
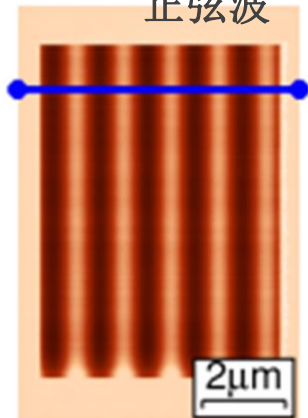
16级棋盘



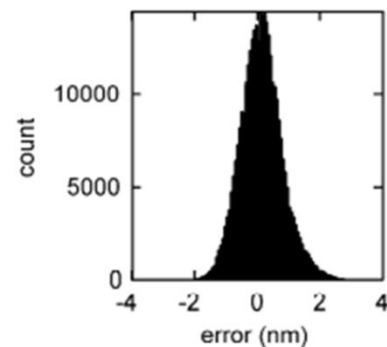
Step size: 1.5 nm



正弦波

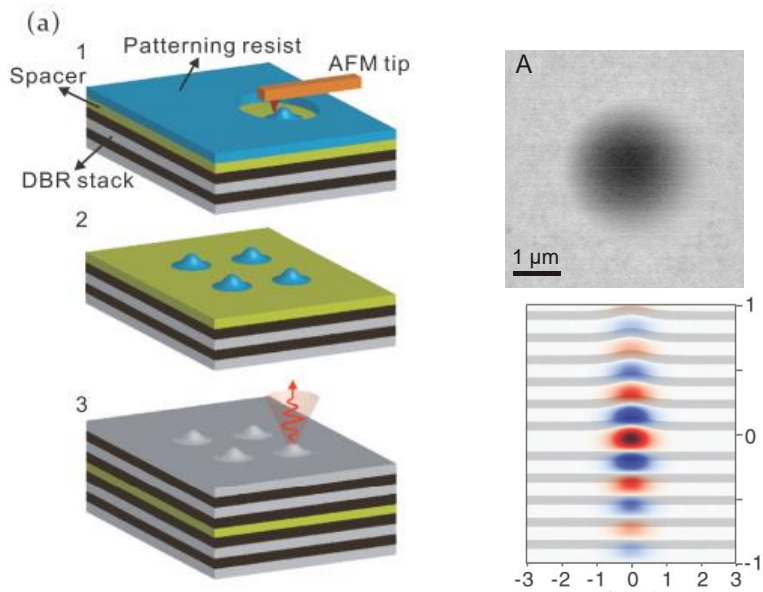


Error $1\sigma < 1\text{ nm}$



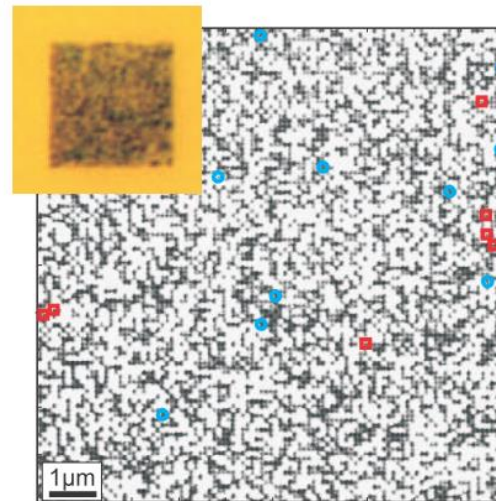
热式扫描探针技术介绍

光学微曲面



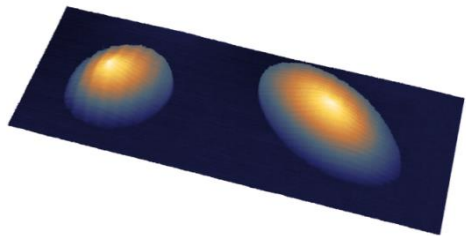
Ding *et al.*, Phys. Rev. B, (2013)

在SOI上的多层直写



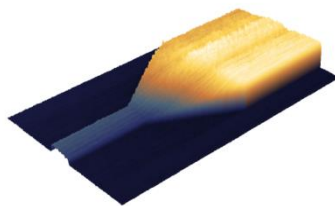
⇒ 安全标识, 全息图, ...
Holzner *et al.*, APL, (2011)

非球面镜

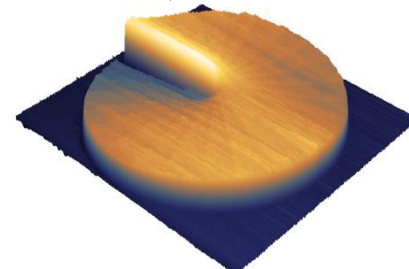


For Scientist, By Scientist

波导结构



螺旋相位板

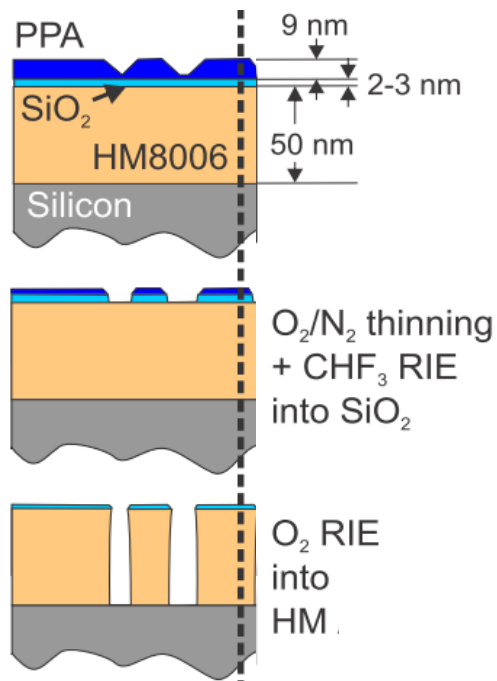


Quantum Design

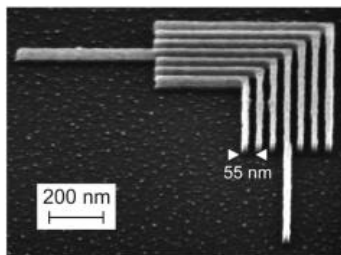


热式扫描探针技术介绍

加工精度



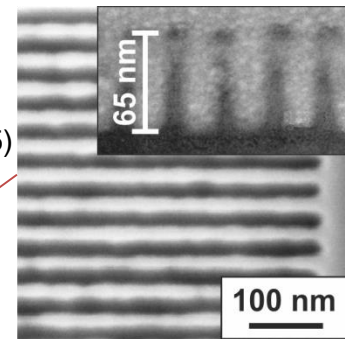
27.5 nm HP in Si



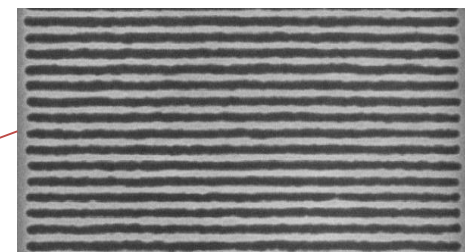
Cheong *et al.*, Nano Letters, (2013)

18.5 nm HP in Si

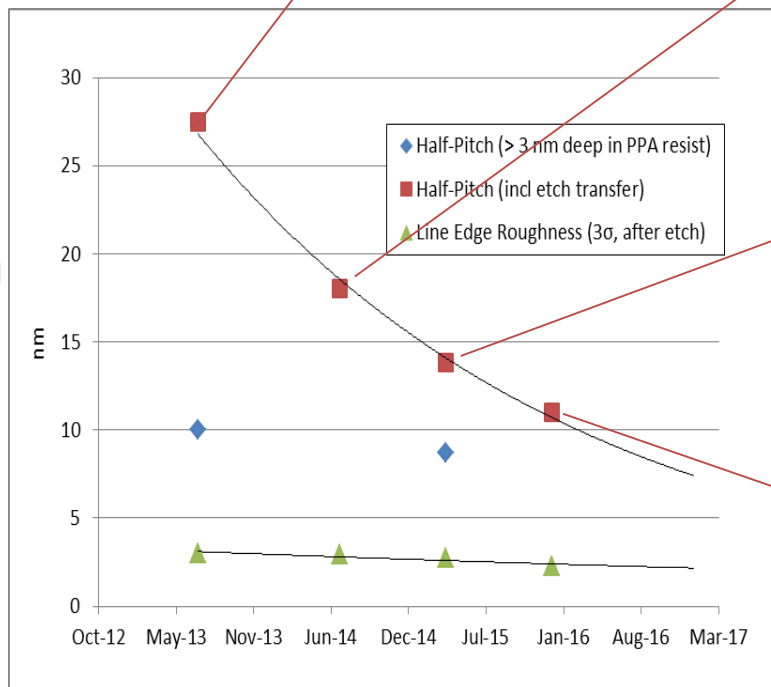
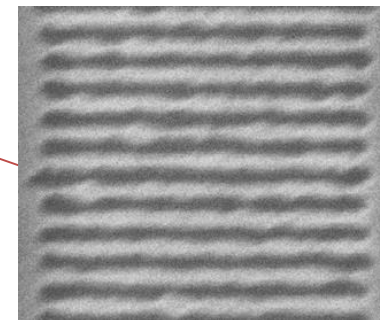
Wolf *et al.*, JVSTB, (2015)



13.8 nm HP in Si



11 nm HP in HM



热式扫描探针技术介绍

直写速度

20 mm/s

直写完成时间: 0.7 s

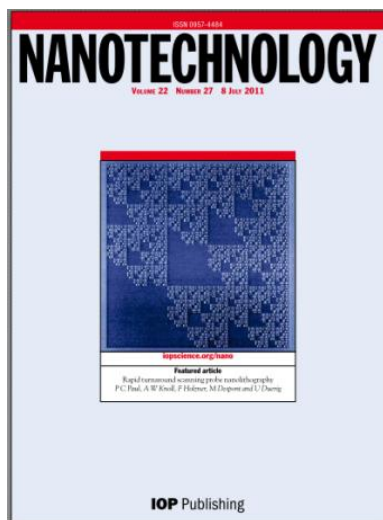
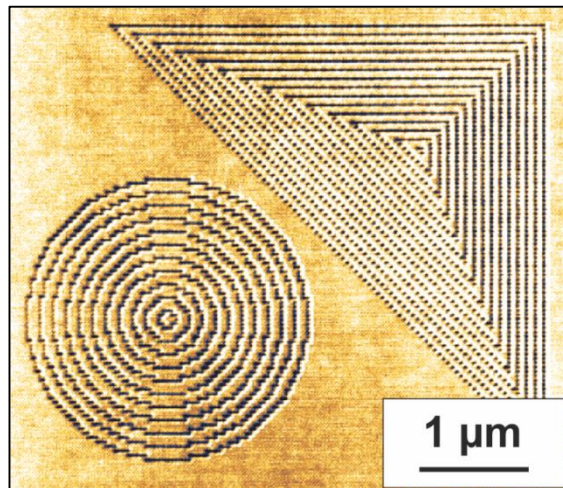
像素速率: 500 kHz

直写速度: 20 mm/s

像素尺寸: 40 nm

图形深度: 4 - 5 nm

直写胶: PPA



1百万像素

无错误

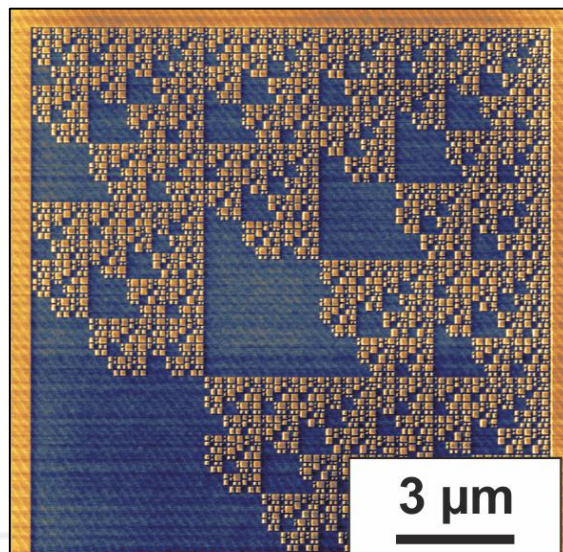
无邻近矫正

直写完成时间: 12 s

像素尺寸: 10 nm

图形深度: 4 - 5 nm

直写胶: PPA



热式扫描探针技术介绍



热式扫描探针技术介绍

无标记套刻

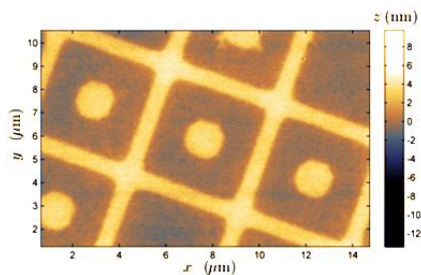
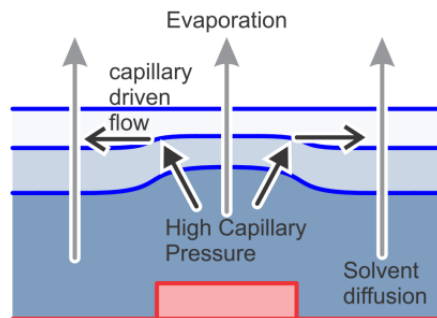
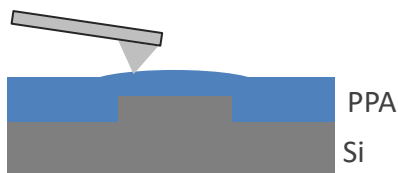
1.) Si片上的微纳结构



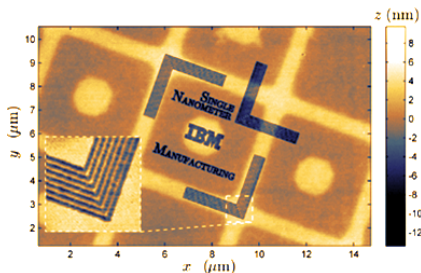
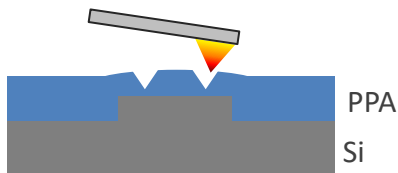
2.) 旋涂后，形貌不明显



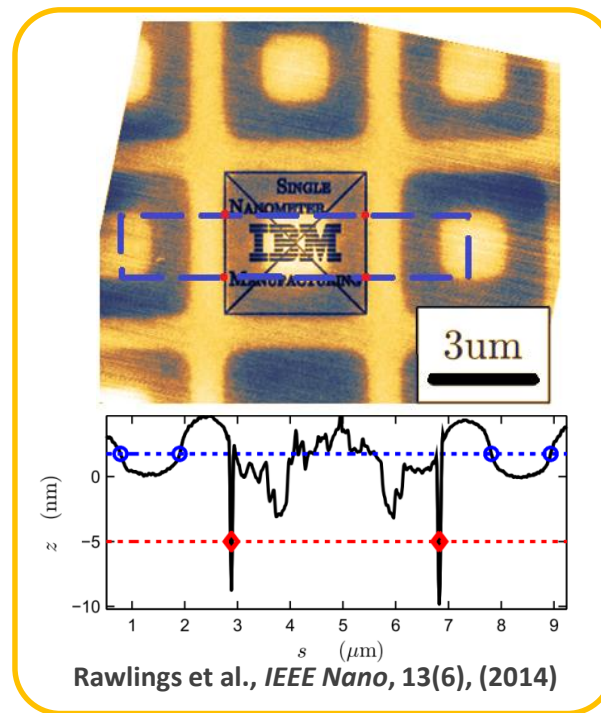
3.) 形貌探测: 冷针扫描



4.) 套刻图形直写: 热针直写



measured overlay error: **3.2 nm**

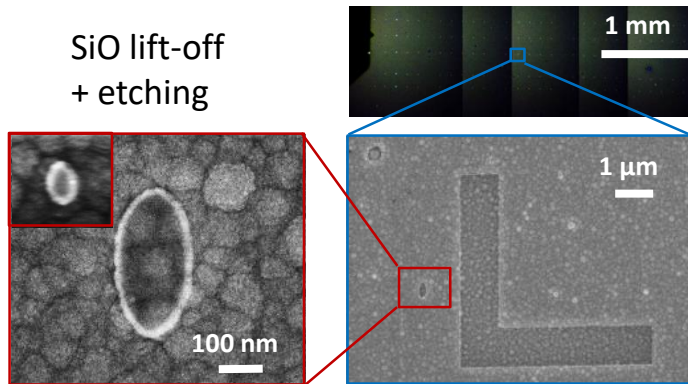


- ▶ 无需标记物直写 <5nm
- ▶ 与其他制备技术兼容，
- ▶ 无需昂贵定位技术
- ▶ 适用于二维材料器件制备

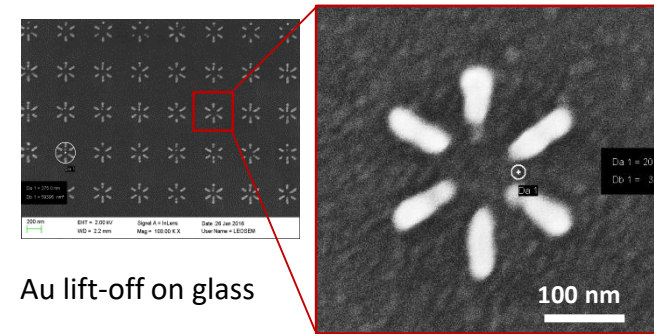
热式扫描探针技术介绍

无临近效应 —— 原来可以更近

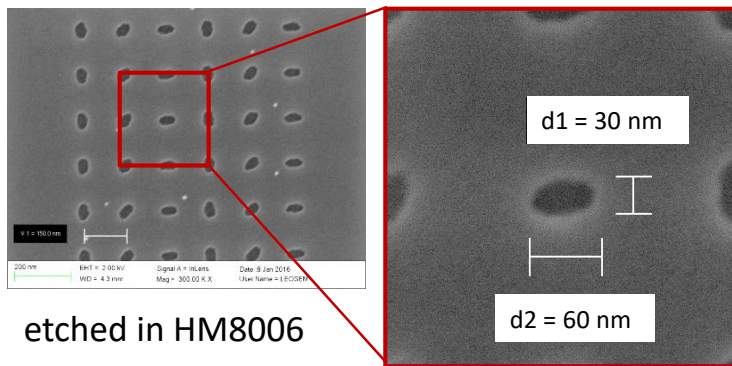
Magnetic ellipses



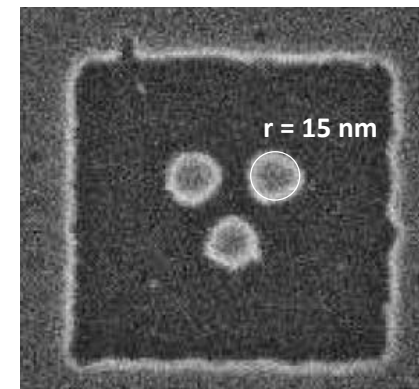
Plasmonic antennas



Rotating Elliptical Quantum Dots



Trimer



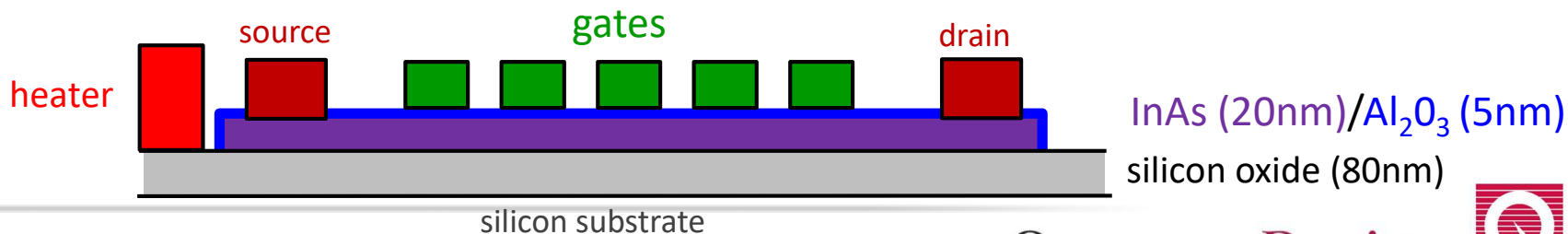
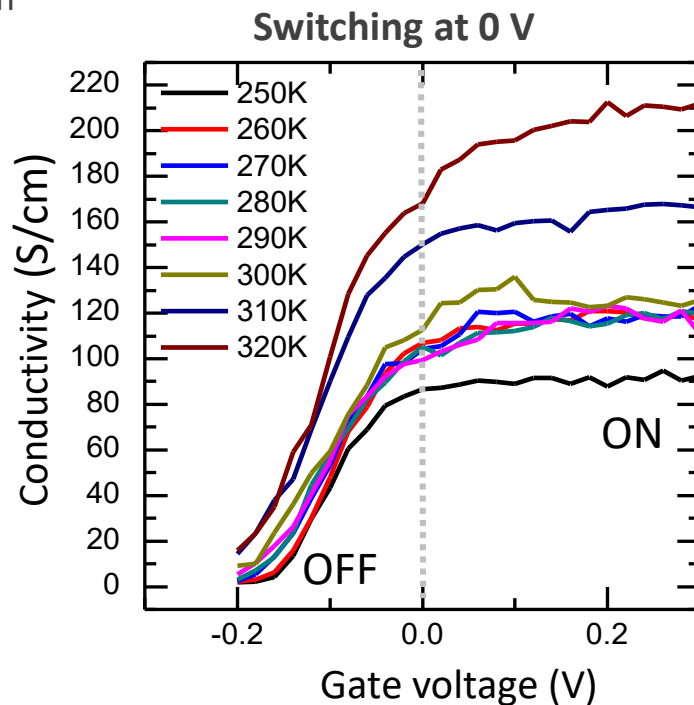
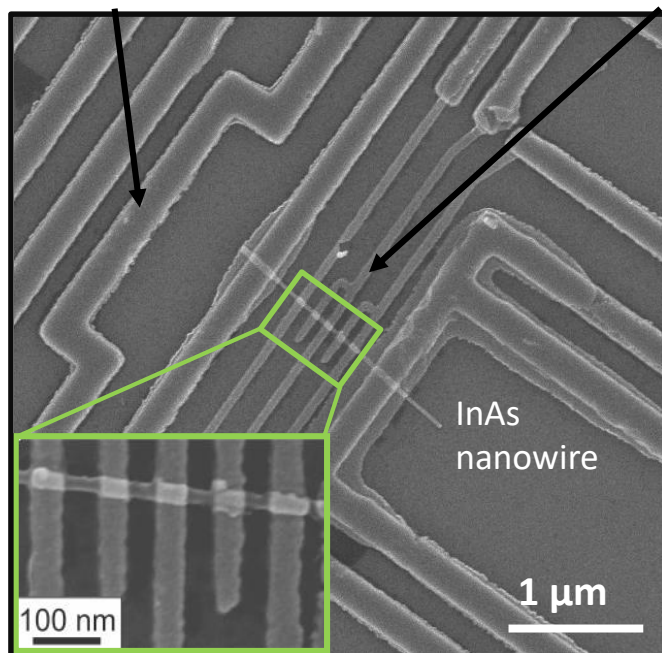
etched in Si

热式扫描探针技术介绍

无电子注入和损伤

- ▶ 50nm电极高精度套刻
- ▶ 栅极材料无荷电效应 → 优越的电学性能

E-Beam lift-off NanoFrazor overlay + lift-off



For Scientist, By Scientist

热式扫描探针技术介绍

兼容各种图形转移技术



2D Etch



- ✓ high aspect ratio
- ✓ high resolution

3D Etch



- ✓ 3D devices
- ✓ stamps for NIL

Lift-Off



- ✓ high resolution
- ✓ metal contacts

Plating



- ✓ shims for injection molding

Assembly



- ✓ placement of nanoparticles⁰⁰

Pires et al.,
Science, 2010

Holzner et al.,
Appl. Phys Lett.,
2011

Wolf et al.,
JVSTB., 2015

Rytka et al.,
PRN, 2014

Holzner et al.,
Nano Lett., 2011

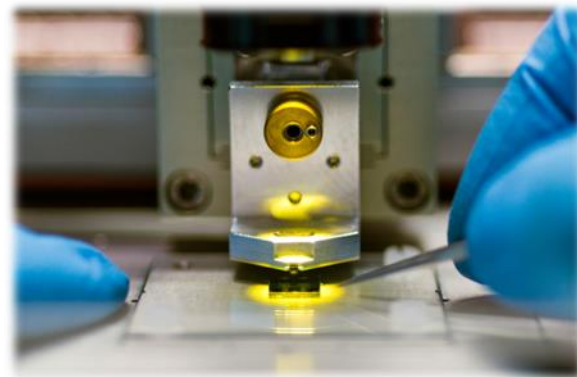
Cheong et al.,
Nano Lett., 2013

纳米光学，光子学

- ◆ 衍射透镜，光栅
- ◆ 非球面微透镜阵列
- ◆ 光学微腔、光子晶体

微电子学，磁学

- ◆ 表面等离子激元，超材料
- ◆ 纳米磁学
- ◆ 纳米电子器件



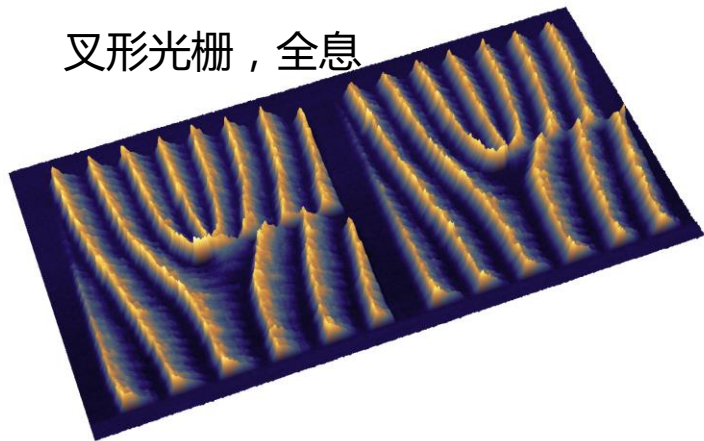
微结构，其他

- ◆ MEMS/NEMS
- ◆ 生物细胞研究
- ◆ 纳米流体控制
- ◆ 纳米颗粒自组装
- ◆ 纳米局部化学反应

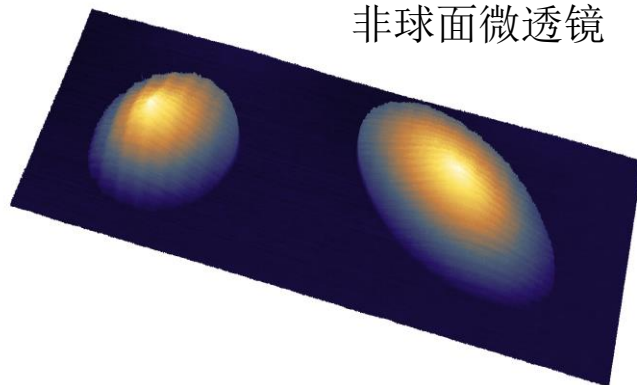
应用领域及案例

纳米光学，光子学

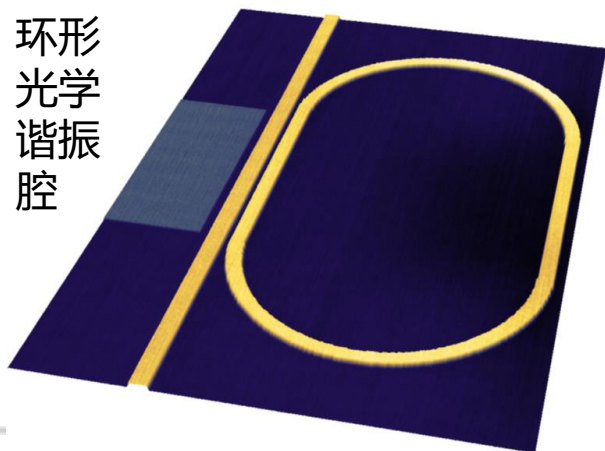
叉形光栅，全息



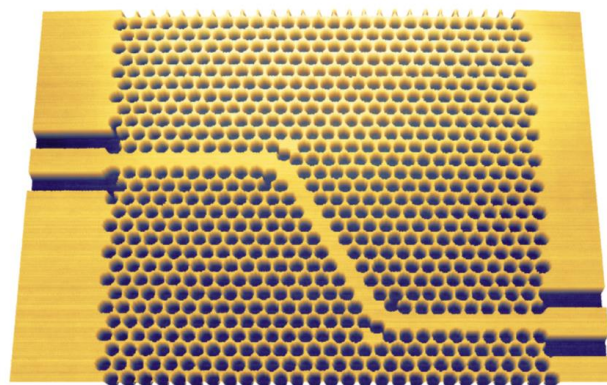
非球面微透镜



环形
光学
谐振腔



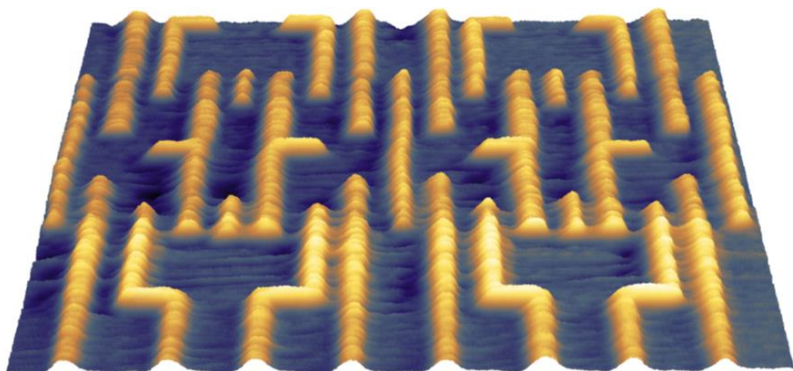
光子
晶体
波导



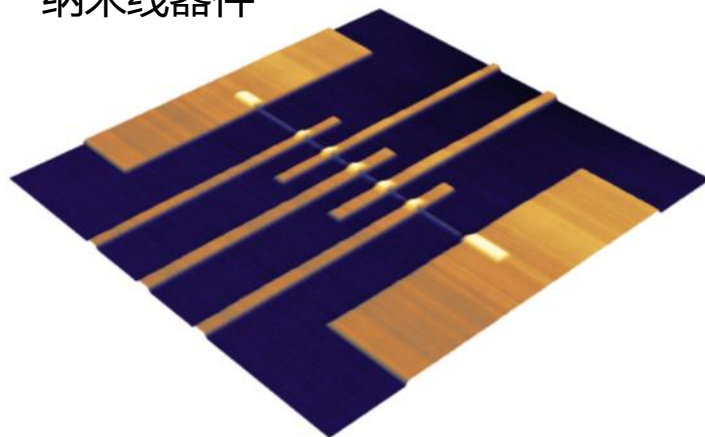
应用领域及案例

纳米电子学，磁学

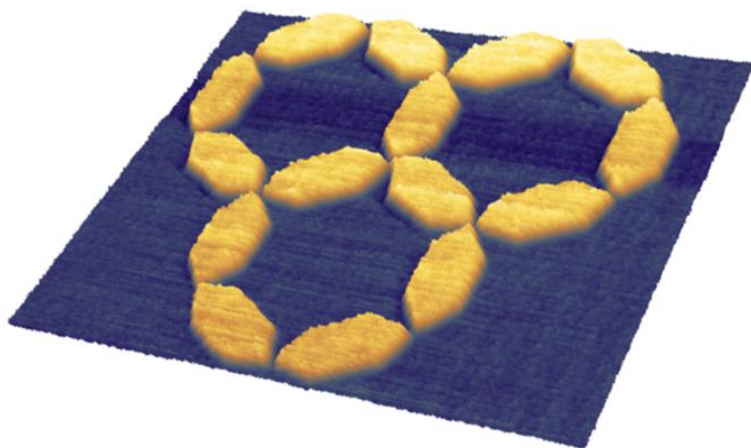
集成电路



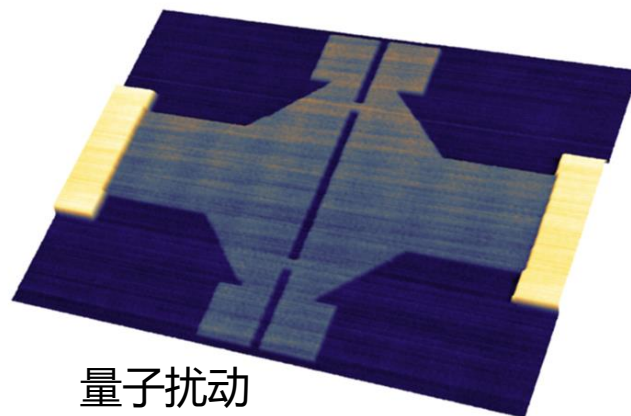
纳米线器件



人工自旋结构



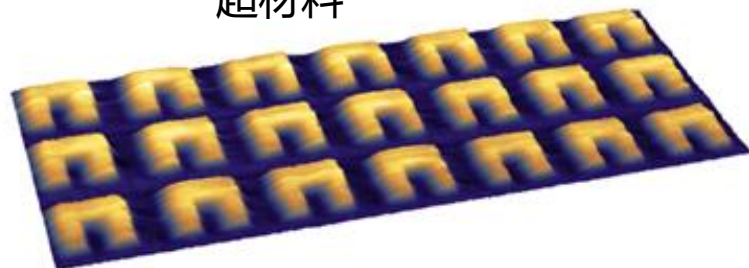
量子扰动
超导探测器



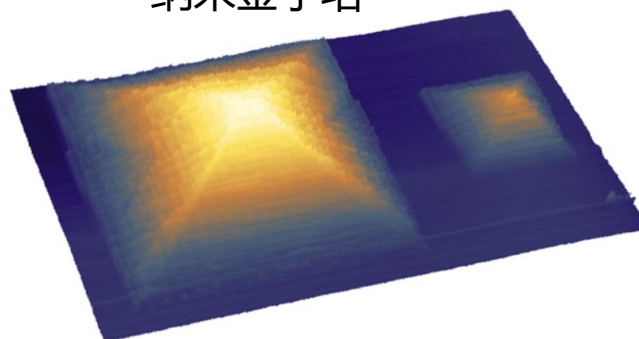
应用领域及案例

等离子体物理及其他

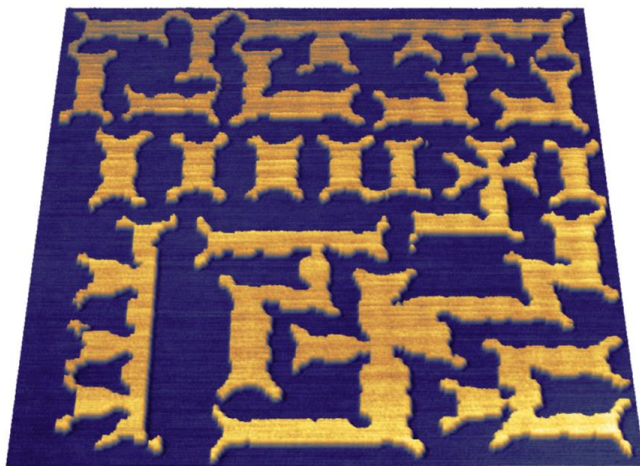
超材料



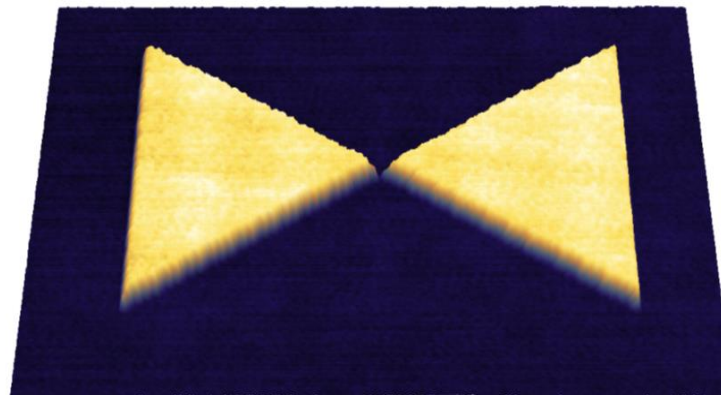
纳米金字塔



OPC掩模



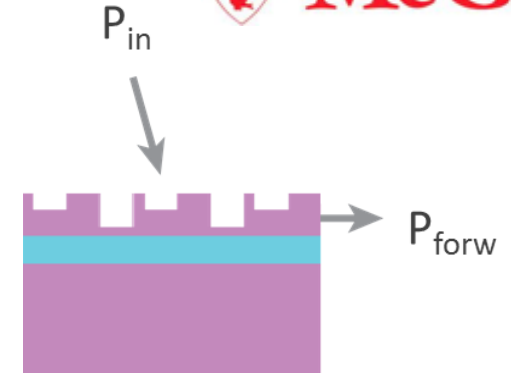
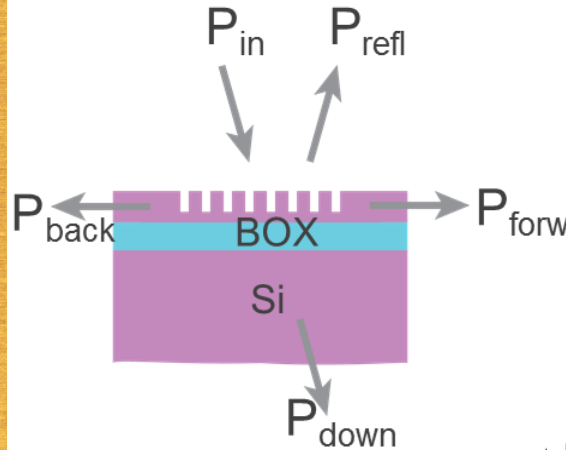
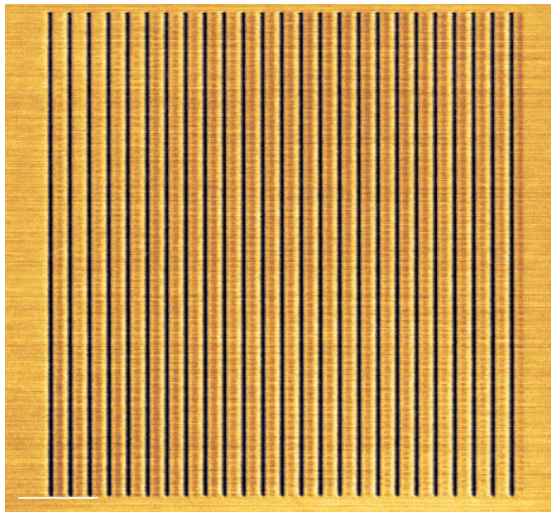
纳米天线



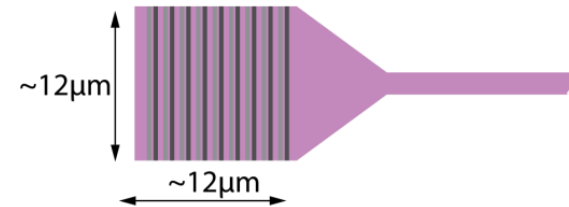
应用领域及案例

12 μm

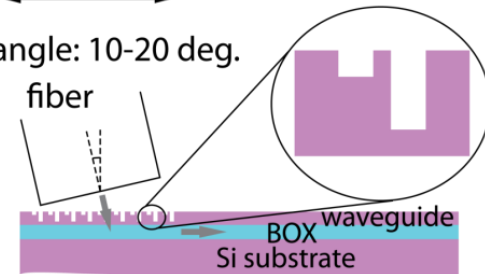
光学耦合立体光栅



损耗显著减少

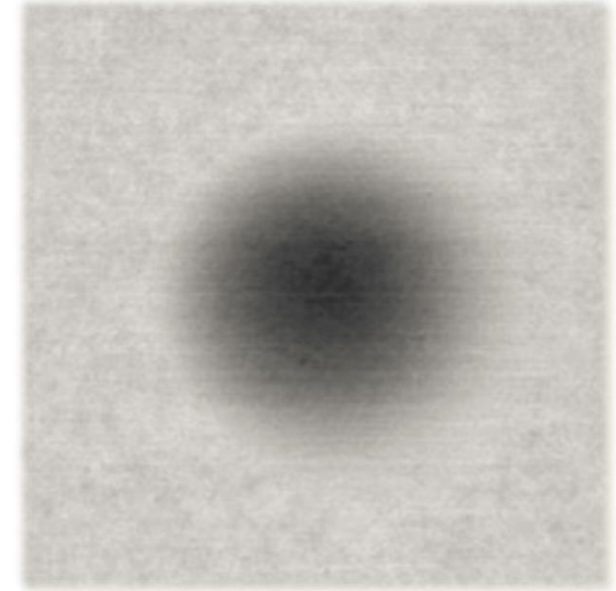
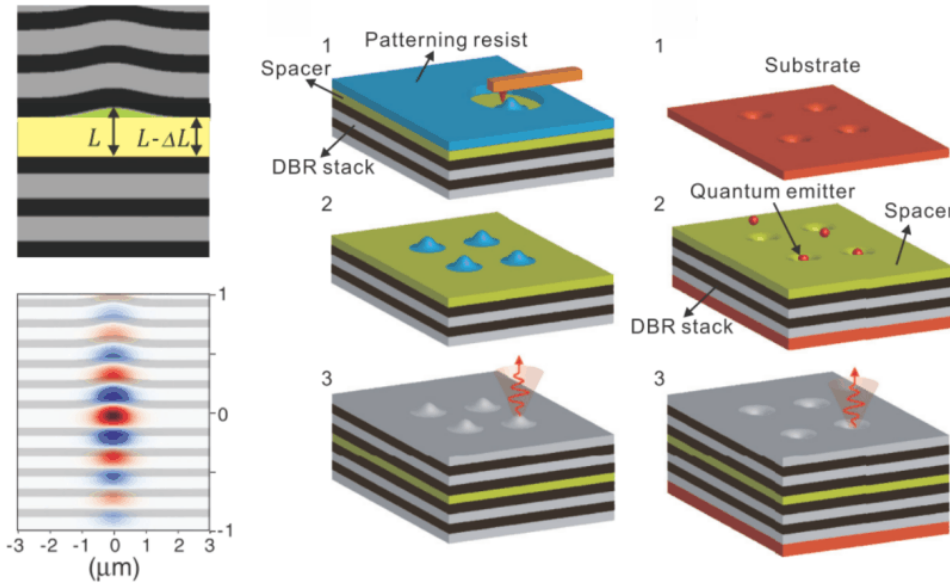


fiber angle: 10-20 deg.



应用领域及案例

• 非球面微透镜阵列



Ding et al., Phys. Rev. B, 2013

光与物质的耦合

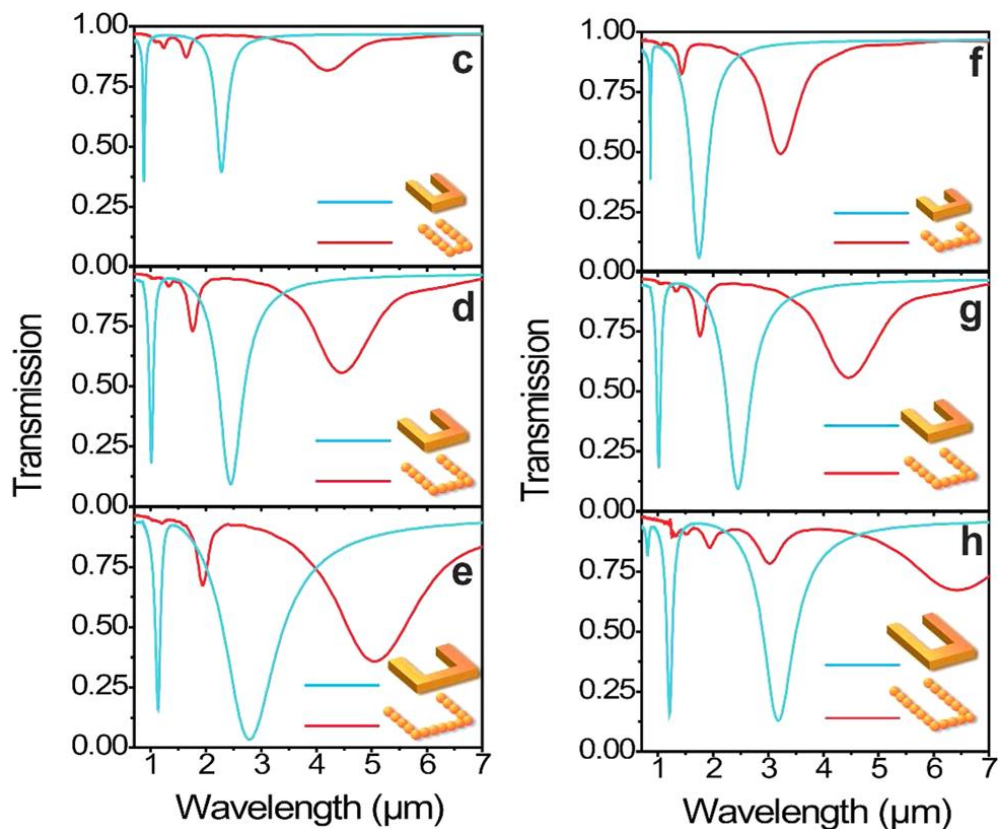
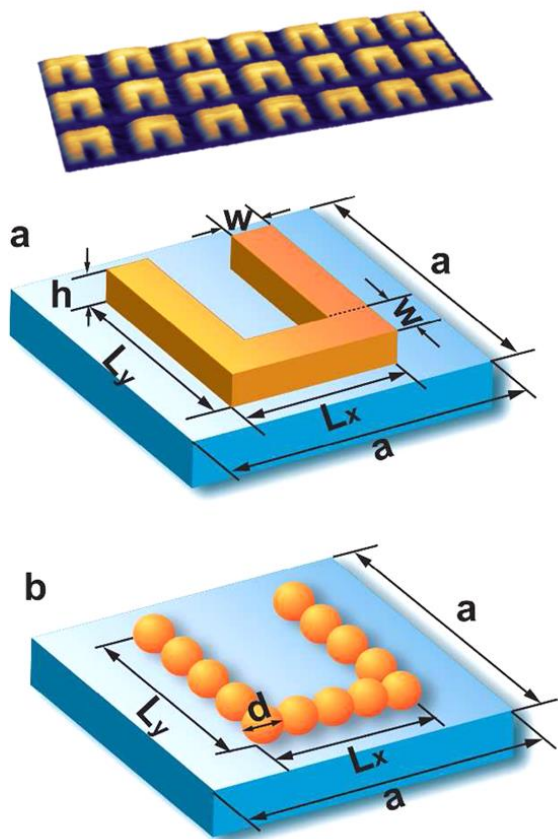
Figure of merit: Q/V , (Q: quality factor of cavity, V: optical mode volume)

High Q/V 可以保证曲面中光场与光学材料的高度耦合

应用：单光子发射器，thresholdless lasing

应用领域及案例

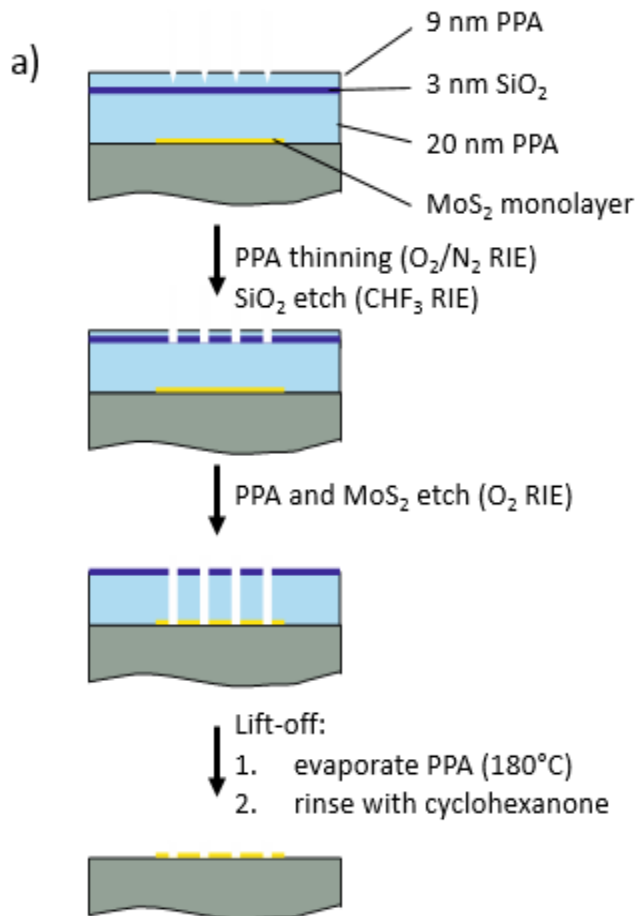
等离子体物理



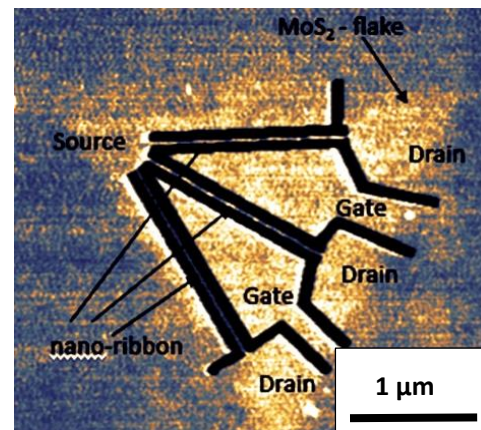
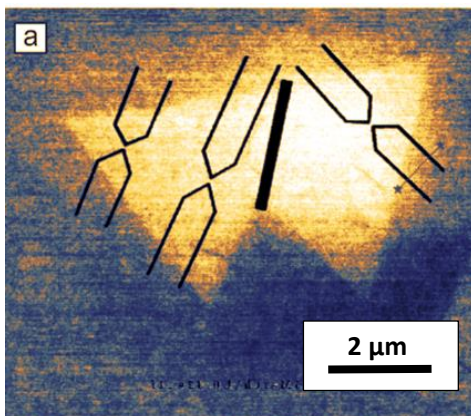
Li et al., ACS Photonics 2014, 1, 228–234

应用领域及案例

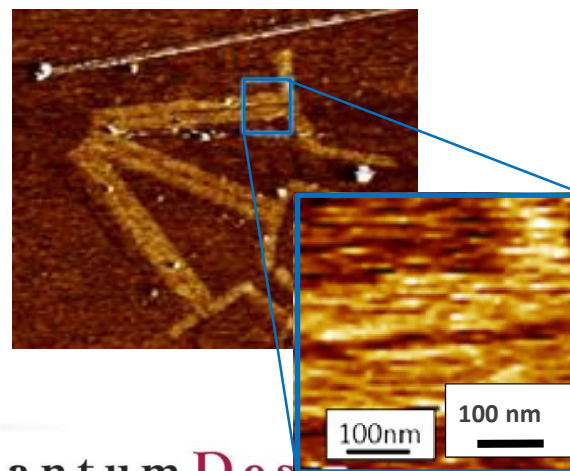
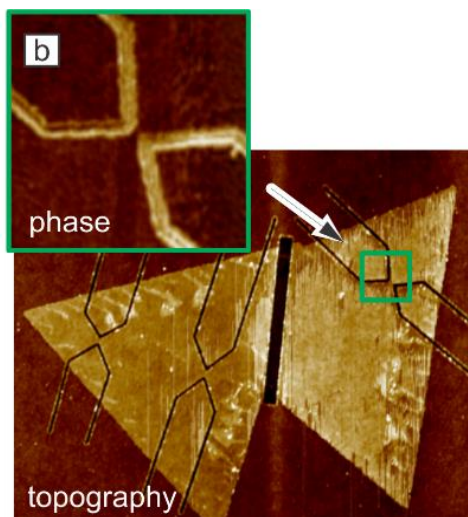
2D 材料器件制备



MoS₂ devices: PPA patterning on flakes using NanoFrazor overlay
Patterns in PPA (NanoFrazor images)



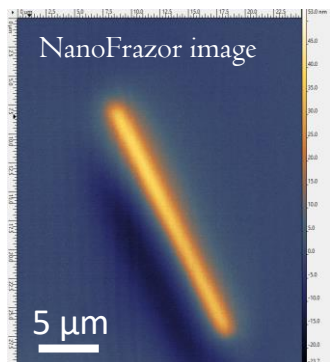
AFM images after etching



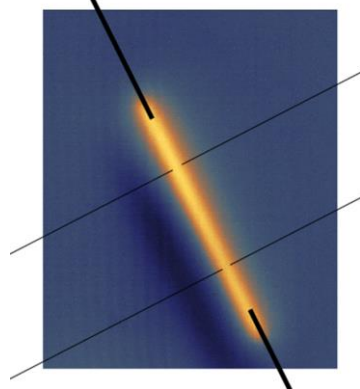
应用领域及案例

纳米线器件制备

1. 涂胶后纳米线的形貌



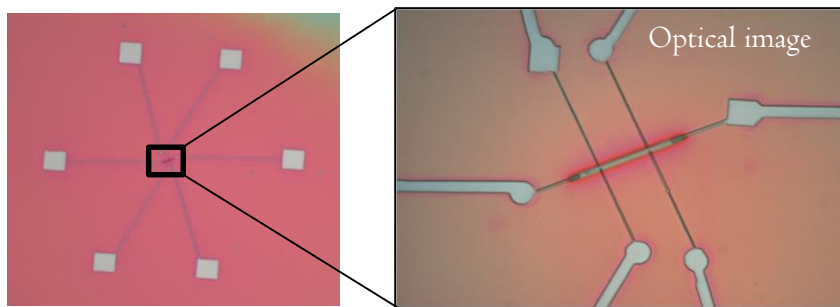
2. 电极设计图与纳米线对准



3. 电极图形直写

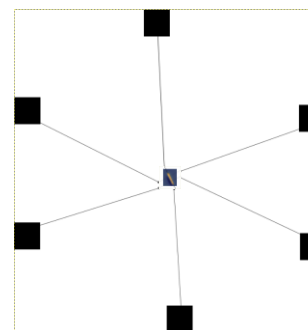


5. 沉积金属并lift off



Marcos Puydinger (Unicamp, Brazil)

4. 接入电极设计



应用领域及案例

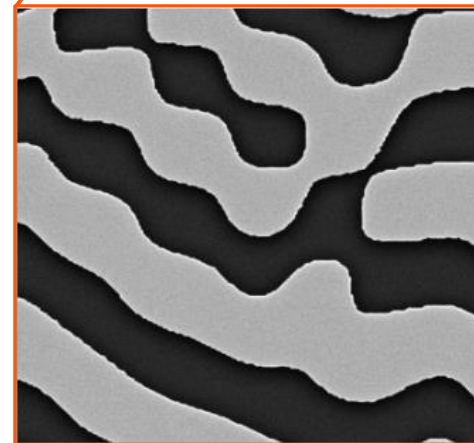
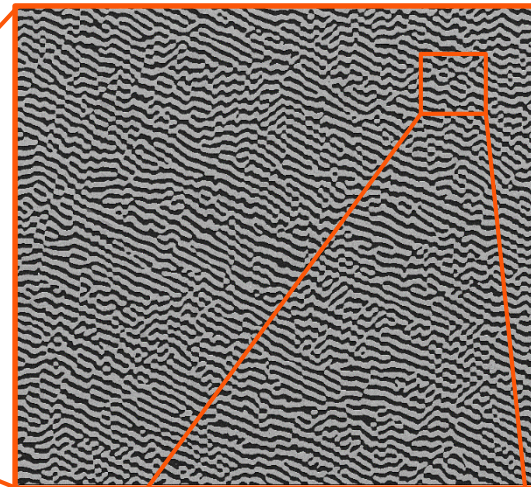
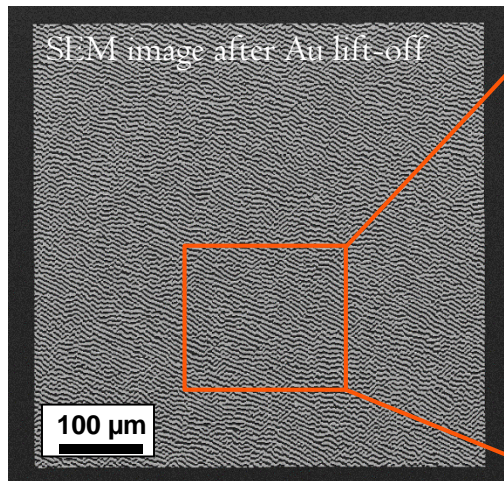
激光全息图制备

功能：

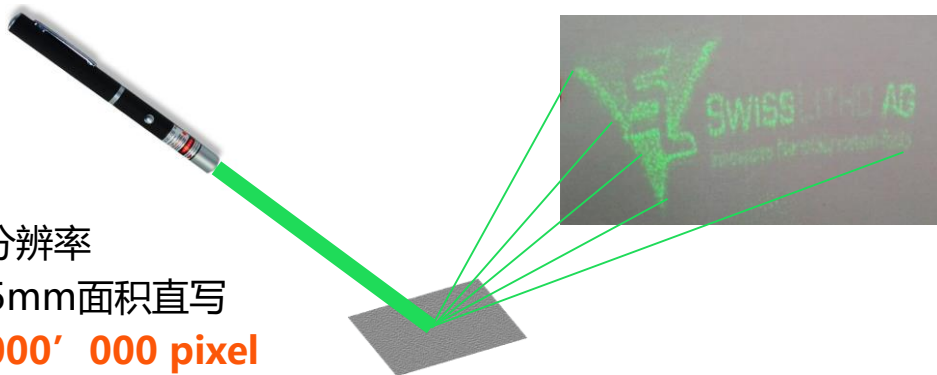
激光照射图形区域，在反射端出现Swisslitho AG公司的logo

应用

- 防伪标识
- 光束控制器件



- 50nm分辨率
- 0.5X0.5mm面积直写
- **100' 000' 000 pixel**

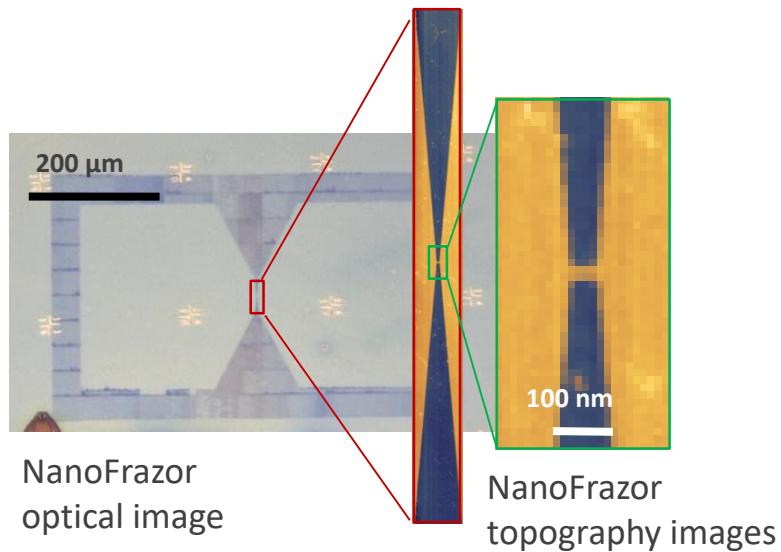


应用领域及案例

石墨烯周期性纳米结构

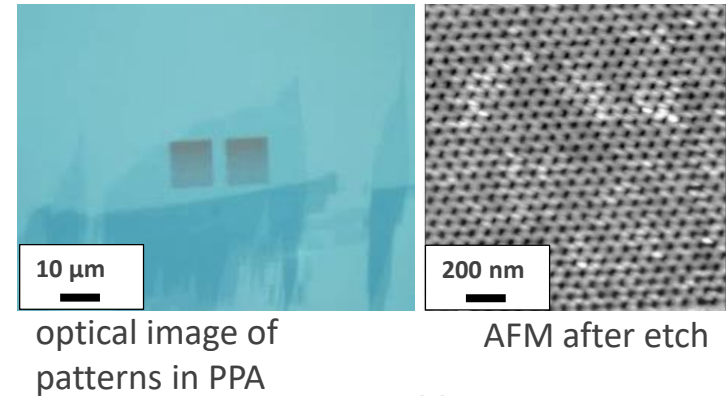
Epitaxial Graphene

nanoribbon and contact pads patterned in PPA
on top of epitaxial grown graphene

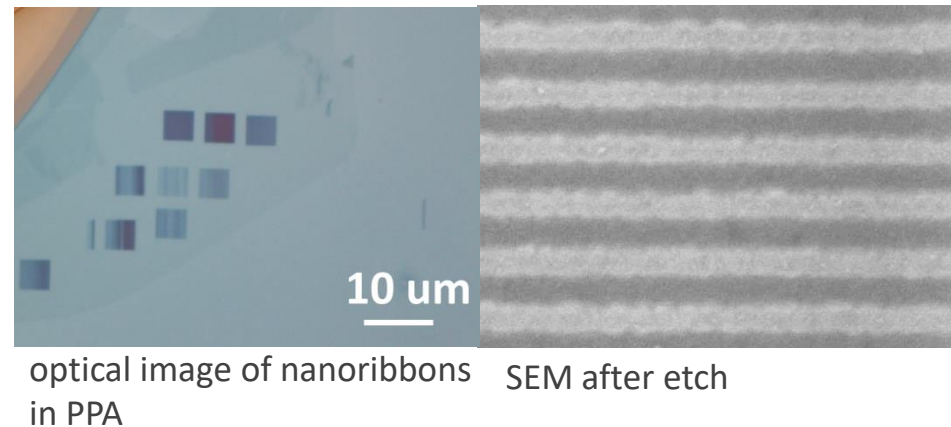


M. Calame (Uni Basel), Z. Wu (SwissLitho)

35 nm antidot pattern



48 nm nanoribbons

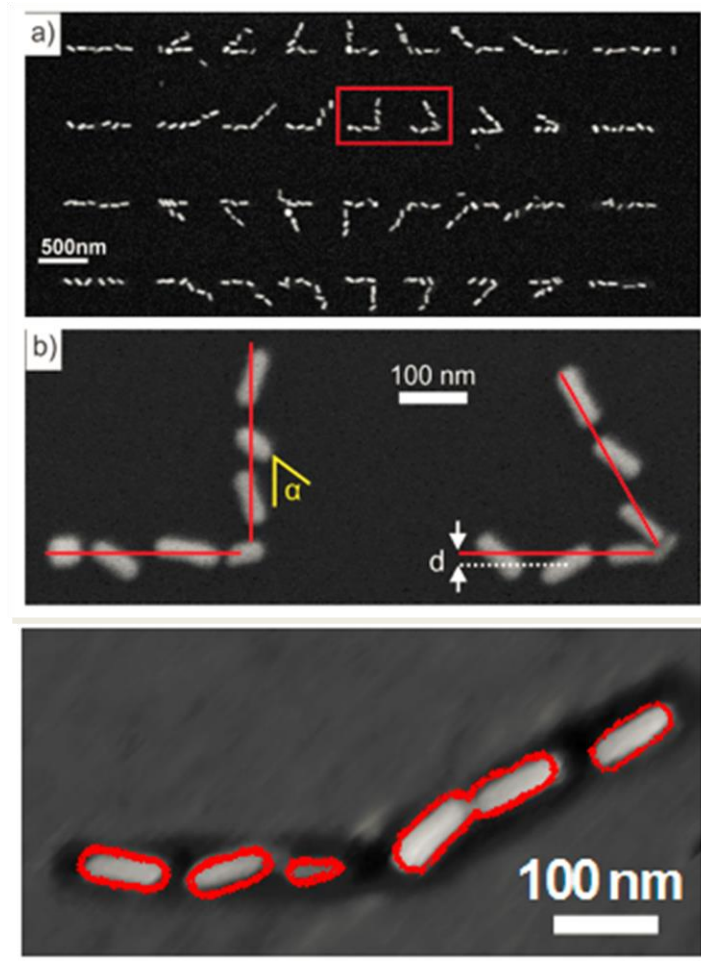
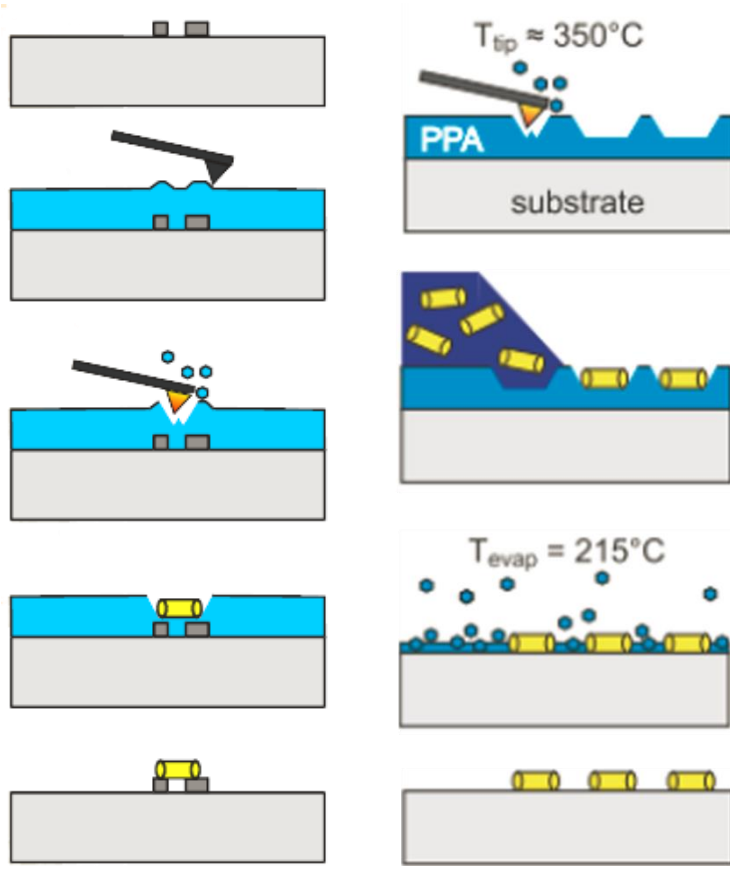


Raman measurements at DTU Copenhagen:
=> indicate that *no doping, no defects* from PPA

A. Cagliari (DTU Copenhagen), S. Bonanni (SwissLitho)

应用领域及案例

纳米颗粒定位，组装



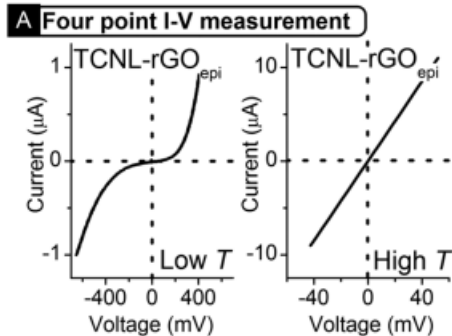
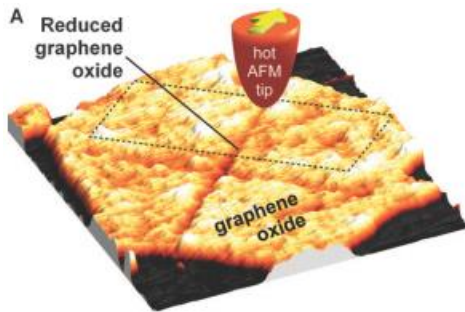
Holzner et al., *Nanoletter*, 11, 3957–3962, (2011)

应用领域及案例

区域热加工与改性

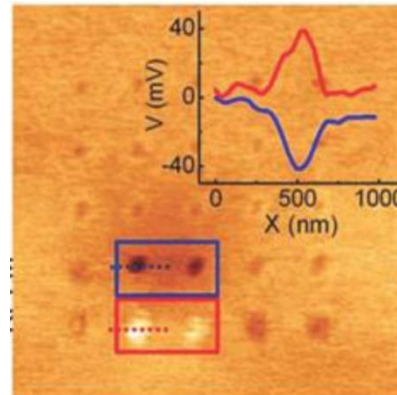
NanoFrazor 的直写针尖在加热时可以实现对热敏感材料的局部加工与改性

氧化石墨烯还原



Wei *et al.*, Science, (2010)

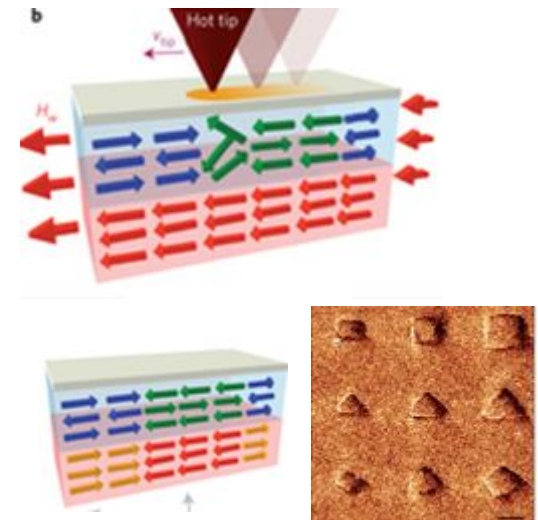
铁电材料



NanoFrazor 可以利用加热的探针在涂敷有铁电薄膜的塑料, Si, 玻璃基片表面, 制备纳米铁电器件。

Kimi *et al.*, Adv. Mat., (2010)

Magnetic nanopatterns



NanoFrazor 可以在可重构磁材料表面利用热探针对局部区域进行磁畴重构, 来制备和研究 magneto-plasmonic

Albisetti *et al.*, Nat Nano, (2016)

总结

	DPN ¹	LAO ²	DLW ³	FIB ⁴	EBID ⁵	EBL ⁶	NF ⁷
连续直写技术	是	是	是	是	是	是	是
平面分辨率优于10nm(Half-pitch)	否	是	否	否	是	是	是
mm/s级高速直写	否	否	是	否	否	是	是
标准图形转移技术支持	否	否	是	否	否	是	是
直接刻写(无需显影)	是	是	否	是	是	否	是
实时形貌探测(高度精度<1nm)	否	是	否	否	否	否	是
3D刻写(高度精度<2nm)	否	否	否	否	否	否	是
闭环刻写技术(刻写+形貌探测)	否	否	否	否	否	否	是
无标记拼接精度<5 nm	否	否	否	否	否	否	是
不损伤样品	是	是	是	否	否	否	是
无需距离修正	是	是	是	是	否	否	是
无需紫外线和高电压	是	是	是	否	否	否	是
设备总价	中等	低	中等	高	中等	高	中等

- 1 Dip Pen NanoLithography 浸蘸笔纳米加工刻蚀
- 2 Local Anodic Oxidation 局部阳极氧化(基于AFM)
- 3 Direct Laser Writing 激光直写技术(基于光刻胶)
- 4 Focussed Ion Beam 聚焦离子束刻蚀(Ga离子源)
- 5 Electron Beam Induced Deposition 电子束诱导沉积
- 6 Electron Beam Lithography 电子束光刻
- 7 NanoFrazor Explore

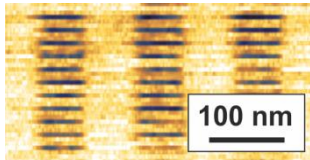
优势：适用于各种生物墨水
 优势：直写
 优势：快速
 优势：3D刻写，适用各种材料
 优势：高分辨
 优势：分辨率高，工艺成熟

缺点：速度慢，分辨率低
 缺点：速度慢
 缺点：分辨率低
 缺点：速度慢，损伤样品
 缺点：速度慢
 缺点：临近效应，使用复杂

总结

与EBL相当的能力

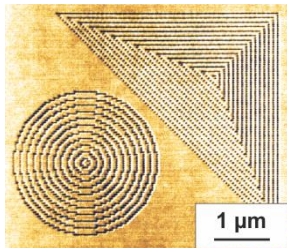
分辨率



< 10nm half-pitch

Holzner, SPIE, 2013

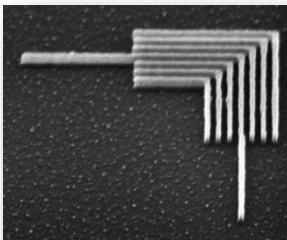
速度



up to 500 kHz, 20mm/s
⇒ < 1 second write time

Paul et al. Nanotech., 2010

图形转移



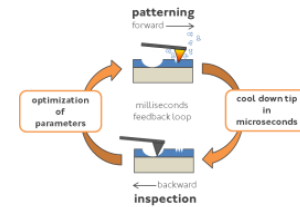
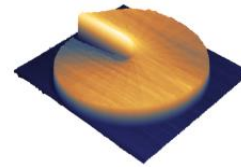
< 15nm
转移到Si 或金属

Cheong, Nano Letters, 2013

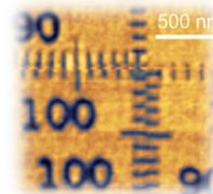
Wolf, JVSTB, 2015

EBL所不具备的独有能力

3D 直写



无需标记物拼接和套刻

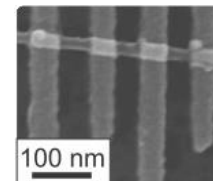


< 5 nm 准确度

Paul, Nanotech., 2011

Rawlings, IEEE, 2014

无电子束损伤



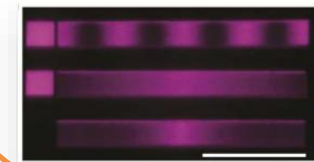
e.g. 为半导体或石墨烯制备纳米电极,

...

⇒ no charging/damage

⇒ 更好的性能

化学图案



局部加热

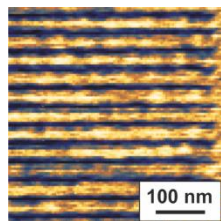
⇒ 局部反应

⇒ 局部表面功能化

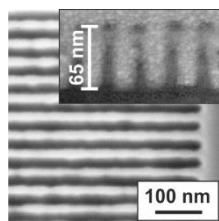
总结

材料

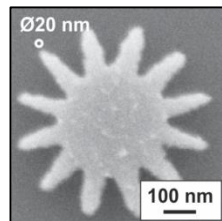
高分子



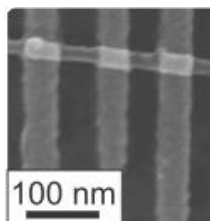
半导体



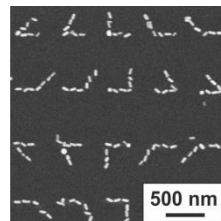
金属



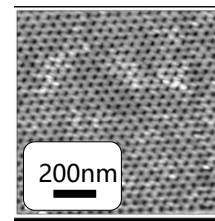
纳米线



纳米颗粒



2D 材料



易用性

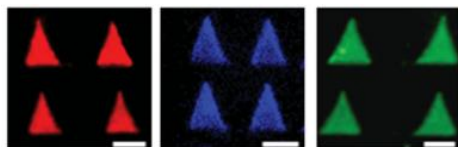
无邻近矫正

无需真空环境

无需高电压

无需特殊实验室配套

多功能性



Streptavidin

Anti-CD3

Fibronectin

局部加热

高度SPM

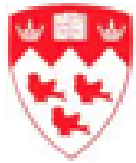
可扩展性

花费

不需专门操作人员 $\approx 80 \$$ /针尖, 每根针尖可连续多天使用

不需单独的软件授权 占地面积小

部分用户



McGill

McGill Microtools Nanofab Montréal,
Canada Prof. Peter Grütter



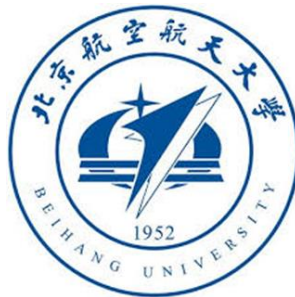
Microsystems Laboratory
Lausanne, Switzerland
Prof. Jürgen Brugger

ETH zürich

Binnig-Rohrer Nanocenter
Prof. Jürg Leuthold



Air Force
Research Laboratory



BUAA,
Prof. Zhao



Melbourne Centre, Victoria,
Australia
Prof. Dr. Saulius Juodkazis



CUNY
ADVANCED
SCIENCE
RESEARCH
CENTER

City University of
New York
Prof. Dr. Elisa Riedo

已发表文章

- Wolf (JVST B 2015) Sub20nm Liftoff and Si Etch and InAs nanowire contacts
- Garcia (**Nat Nano** 2014) Advanced scanning probe lithography
- Rawlings (IEEE Nano 2014) Nanometer accurate markerless pattern overlay using thermal Scanning Probe Lithography
- Holzner (SPIE EMLC 2013) Thermal Probe Nanolithography
- Cheong (**Nanoletters** 2013) Thermal Probe Maskless Lithography for 27.5 nm Half-Pitch Si Technology
- Fei Ding (PhysRevB 2013) Vertical microcavities with high Q and strong lateral mode confinement
- Carrol (Langmuir 2013) Fabricating Nanoscale Chemical Gradients with ThermoChemical NanoLithography
- Paul (Nanotechnology 2012) Field stitching in thermal probe lithography by means of surface roughness correlation
- Kim (**Advance Mat** 2011) Direct Fabrication of Arbitrary-Shaped Ferroelectric Nanostructures on Plastic, Glass, and Silicon Substrates
- Holzner (APL 2011) High density multi-level recording for archival data preservation
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- Wang (**Adv Funct Mat** 2010) Thermochemical Nanolithography of Multifunctional Nanotemplates for Assembling Nano-Objects
- Wei and King (**Science** 2010) Nanoscale Tunable Reduction of Graphene Oxide for Graphene Electronics
- Pires (**Science** 2010) Nanoscale 3DPatterning of Molecular Resists by Scanning Probes
- Knoll (**Adv Materials** 2010) Probe-Based 3-D Nanolithography Using SAD Polymers
- Fenwick (**Nat Nano** 2009) Thermochemical nanopatterning of organic semiconductors
- Lee (**Nanoletters** 2009) Maskless Nanoscale Writing of Nanoparticle-Polymer Composites and Nanoparticle Assemblies using Thermal Nanoprobes
- Nelson (APL 2006) Direct deposition of continuous metal nanostructures by thermal dip-pen nanolithography

新产品发布

NanoFrazor Explore



最大加工面积：100×100 mm
最大写场尺寸：60 × 60 μm
最大加工速度：20mm/s
推荐加工精度：25 nm

NanoFrazor Scholar



最大加工面积：30 × 30 mm
最大写场尺寸：40 × 40 μm
最大加工速度：10 mm/s
推荐加工精度：30 nm

Quantum Design China

By Scientist, For Scientist



Thank you!

样品制备免费开放，详情请咨询：

info@qd-china.com

www.qd-china.com

010-85120280



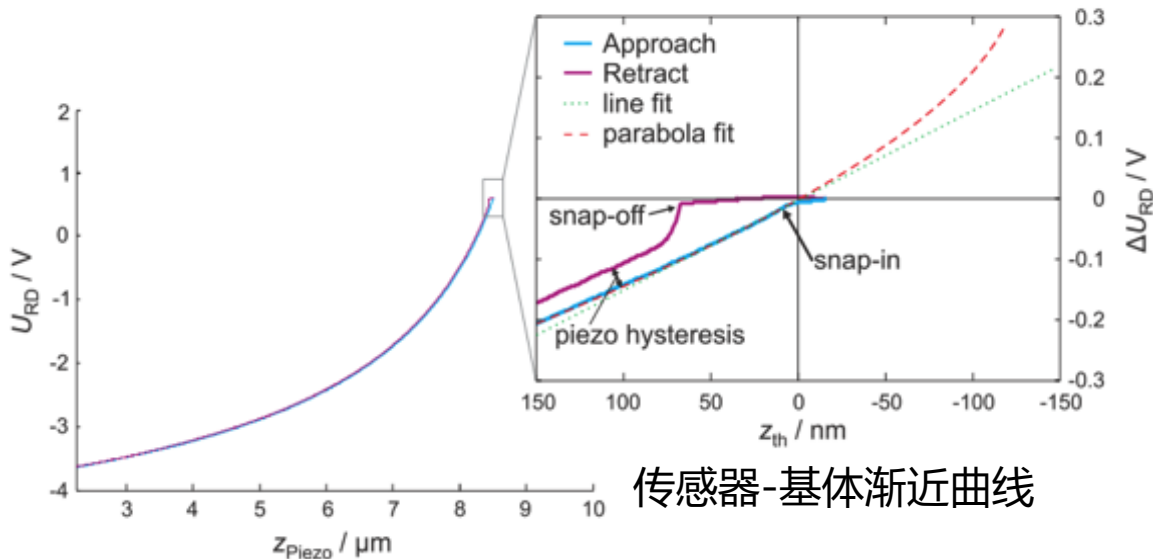
热式扫描探针技术介绍

热导感应和成像



第二个微加热器在侧臂上，作为热传感器

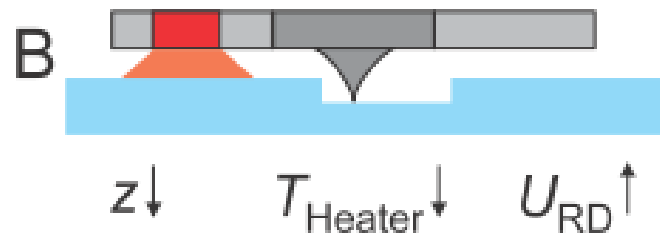
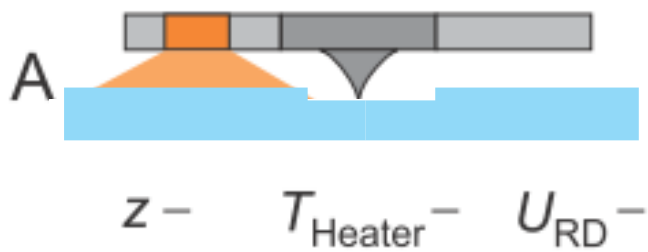
传感器电学信号



传感器-基体渐近曲线

传感器位置

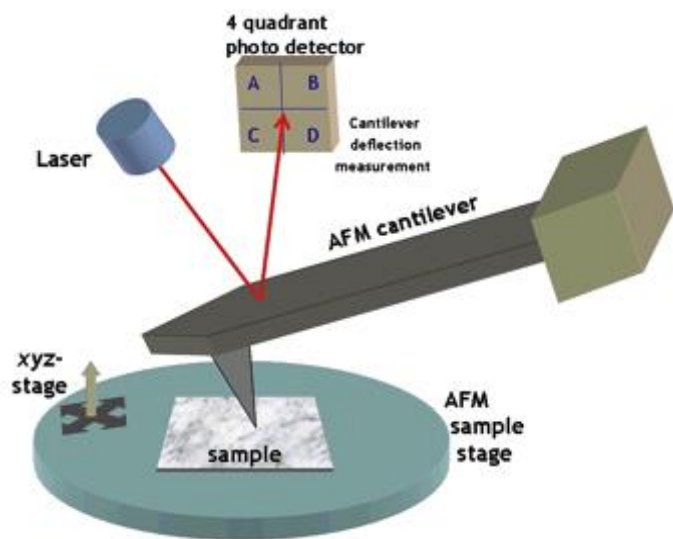
热传感器形貌读取: 灵敏度 0.1 nm



与AFM技术对比

快速直写与成像模式

典型 AFM 设置:



扫描速度被以下因素限制

- ◆ 针尖高度反馈: 像素时间 $\sim Q/f$
- ◆ $Q \sim 300; f \sim 300 \text{ kHz} \Rightarrow 1 \text{ ms}$
- ◆ \Rightarrow 小悬臂

Swisslitho模式:

磨损小-半接触模式

软悬臂 $\sim 0.1 \dots 1 \text{ N/m}$

$Q < 5$



成像速度仅由传感器带宽限制 ($\sim 6 \mu\text{s}/\text{pixel}$)

图形拼接

拼接精度

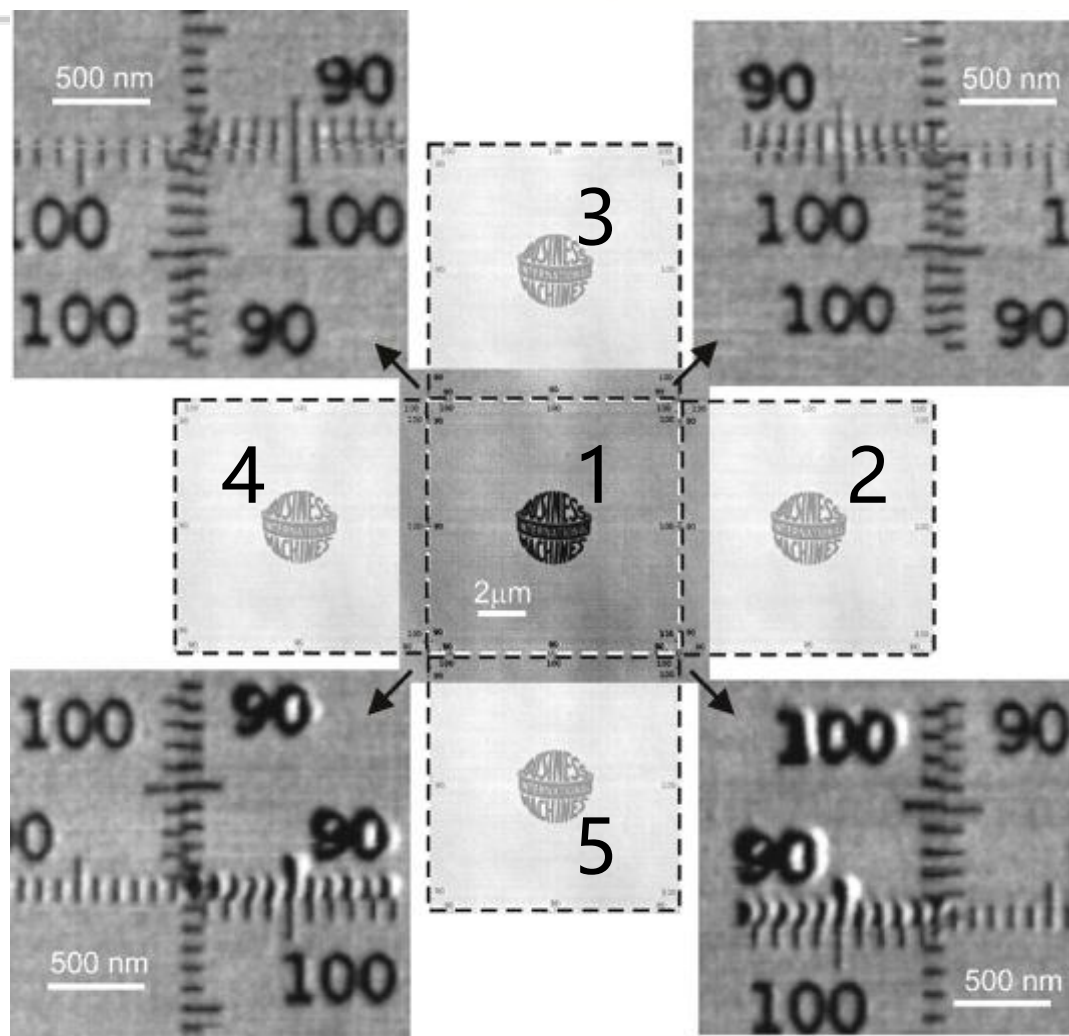
5 nm 拼接误差

由压电位移台精度决定

10 μm 直写区域,

1100 x 1100 pixels

1 μm 拼接边界



图形转移 I

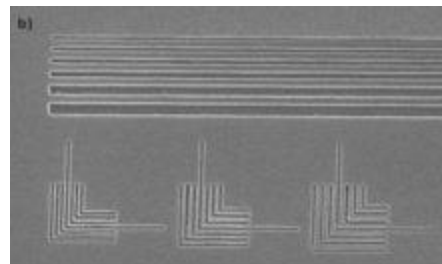
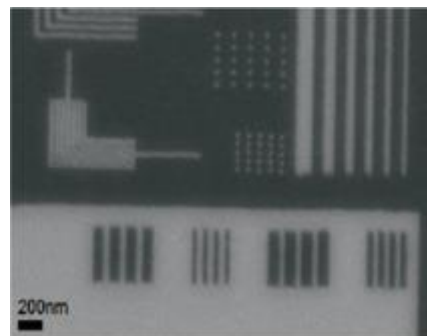
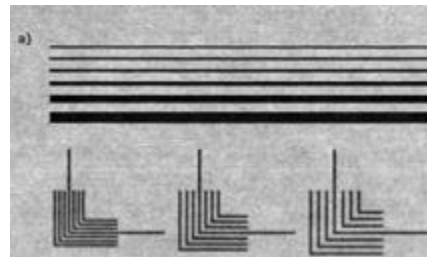
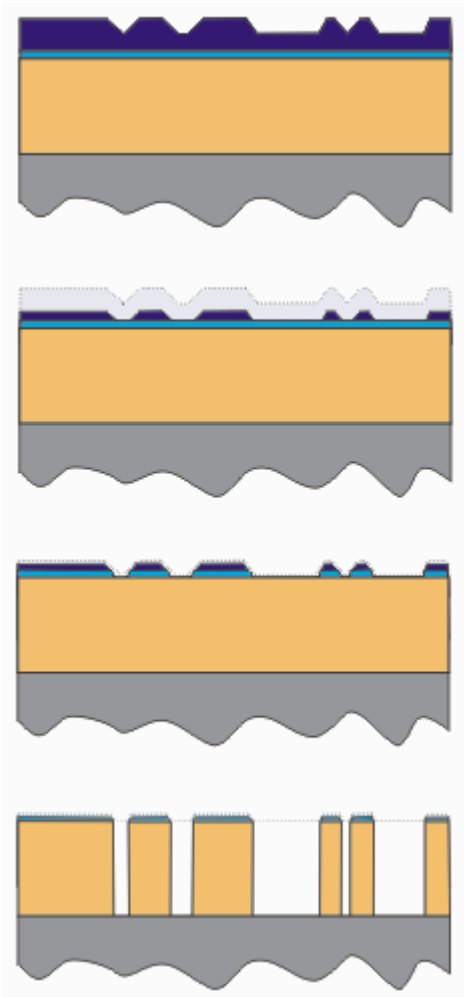
RIE+硬模板

20nm PPA
4nm SiO₂
50nm JSR HM8006

Step 1:
N₂/O₂ RIE thinning

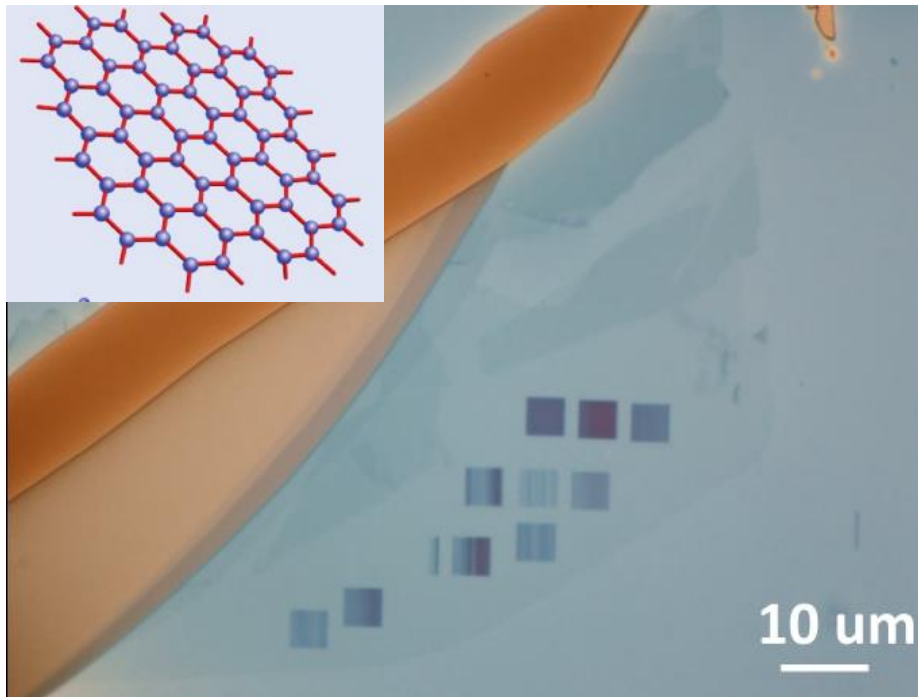
Step2:
CHF₃ RIE into SiO₂

Step3:
O₂ RIE into HM8006



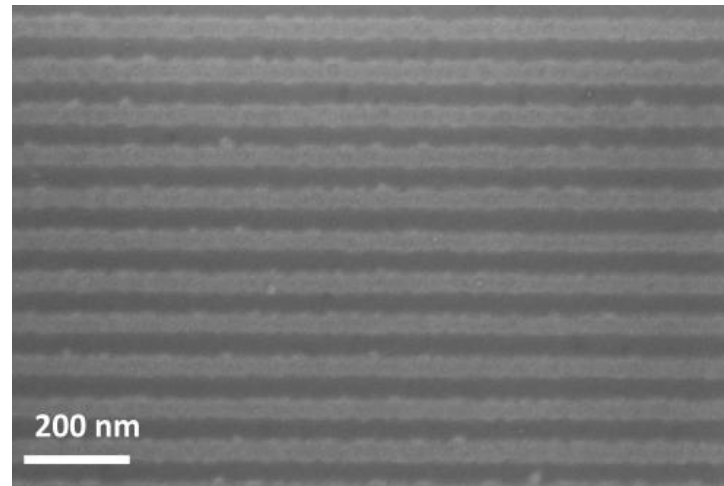
Cheong et al., Nano Letters, **13(9)**, 4485-4491, (2013)

图形转移-石墨烯

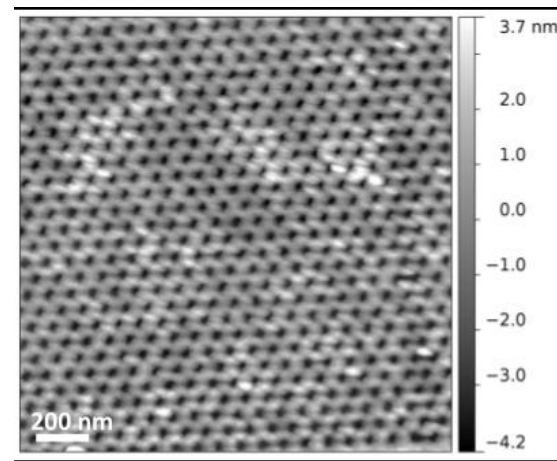


- PPA on 石墨烯
- RIE 图形转移到石墨烯
- 拉曼检测:没有PPA引起的掺杂或缺陷

Alberto Cagliani, DTU Copenhagen



48nm 宽条带

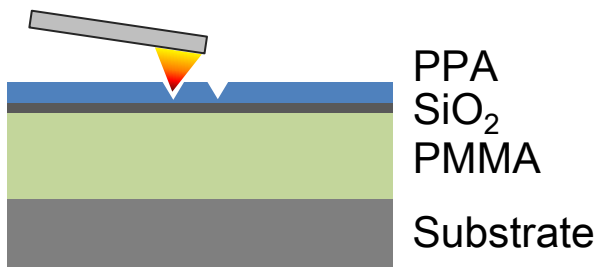


35nm 直径空洞
Quantum Design

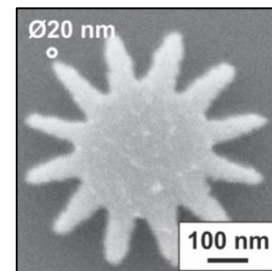
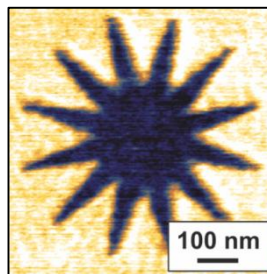


图形转移 II

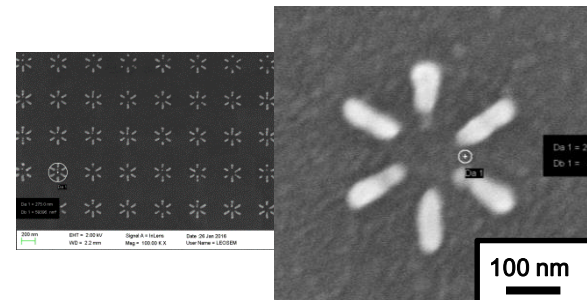
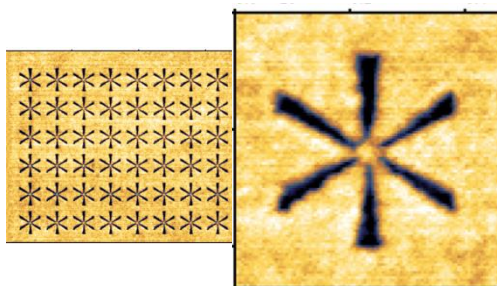
RIE+硬模板+剥离



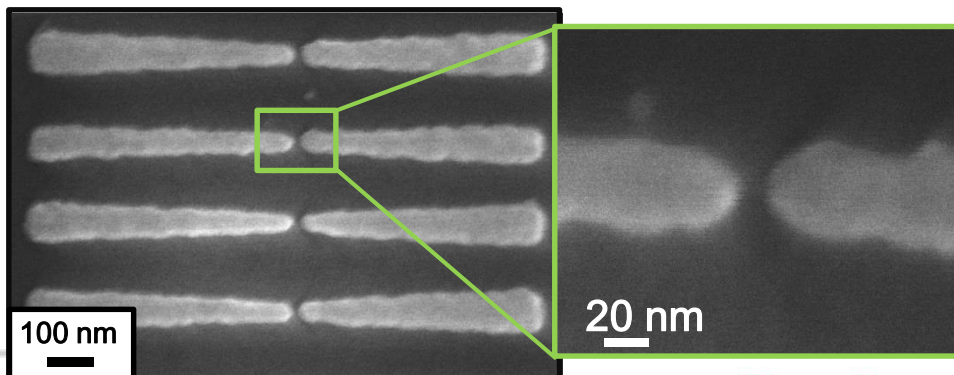
after t-SPL in PPA after lift-off with 30 nm Ni



Wolf et al., JVSTB, (2015)

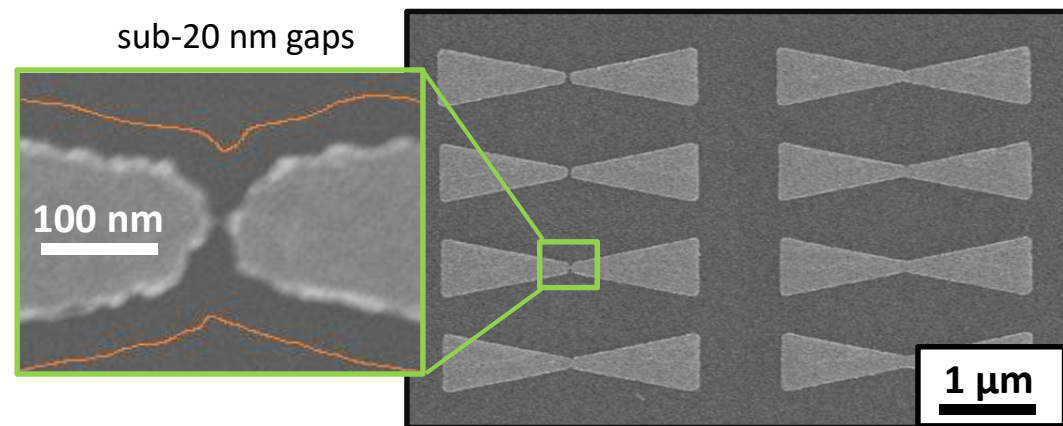
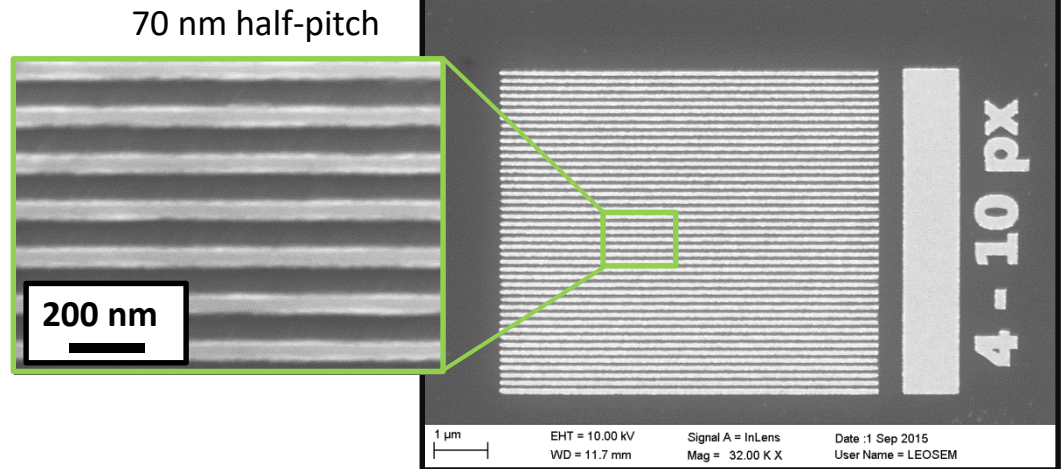
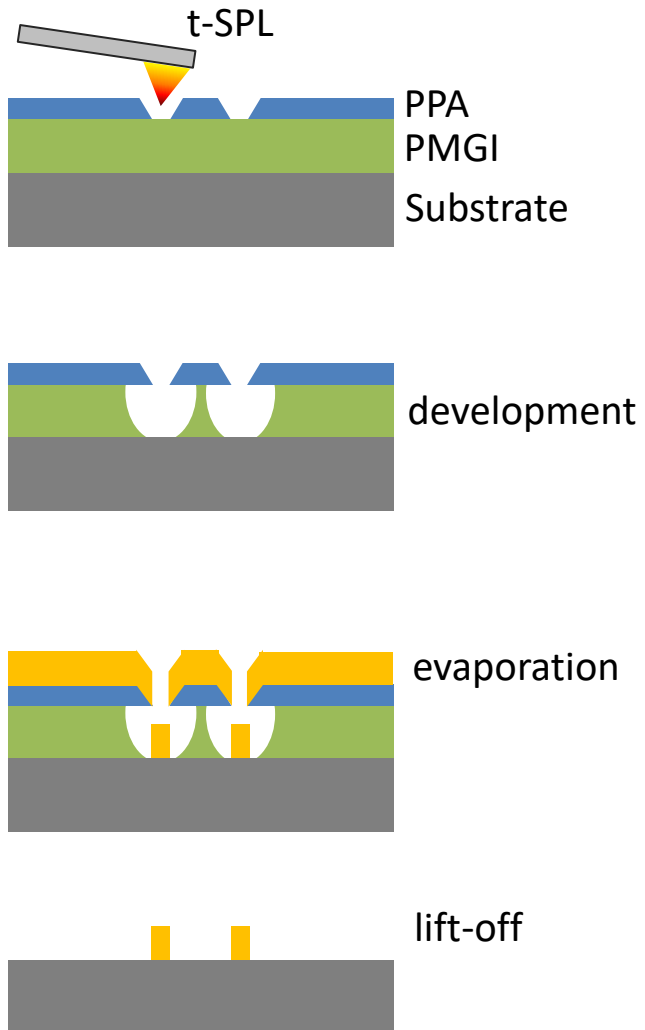


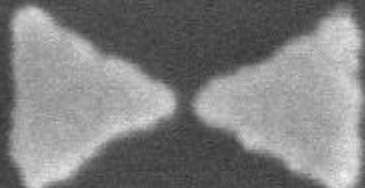
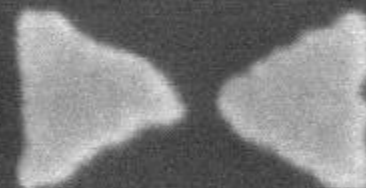
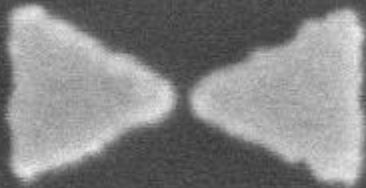
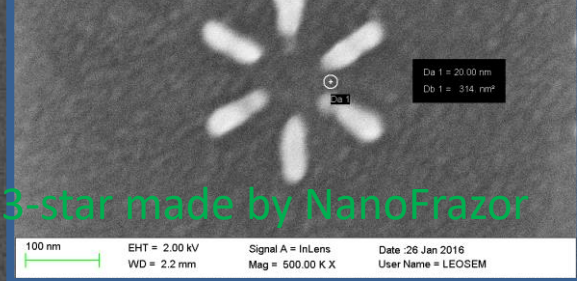
Bow tie antennas (30 nm Au)



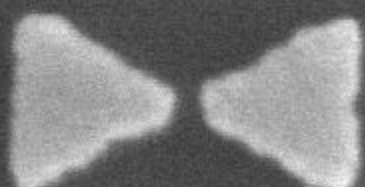
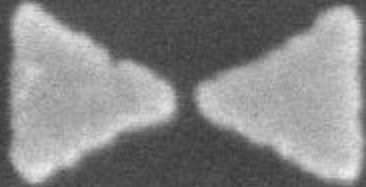
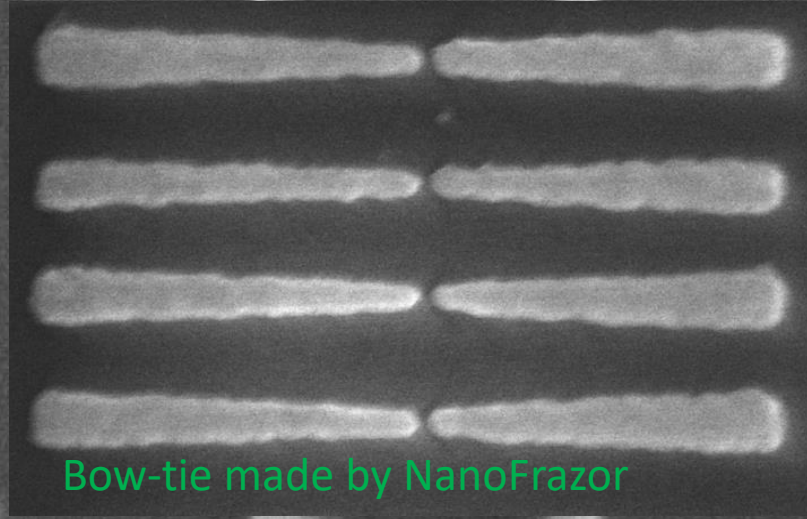
图形转移 II

RIE+硬模板+剥离





Bow-tie made by EBL



HV	WD	Mag	Det	VacMode
10.0 kV	8.9 mm	100000x	LFD	Low vacuum

1.0 μm

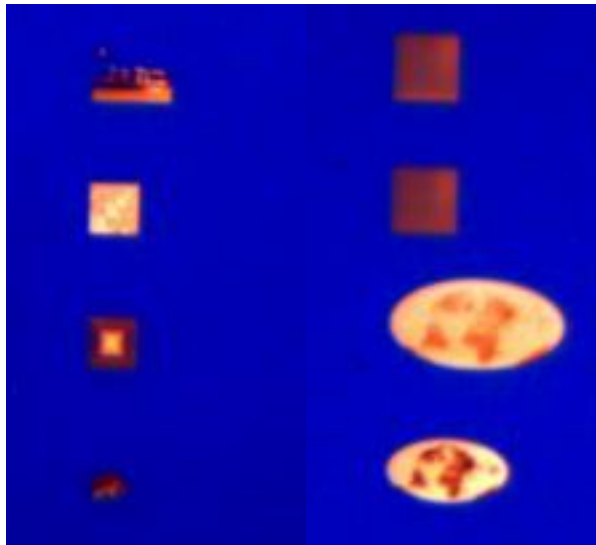
WAMRC-TAU

图形转移 III 反向模板+注射成型

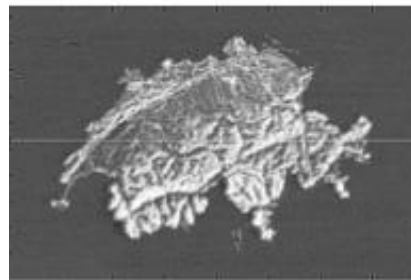
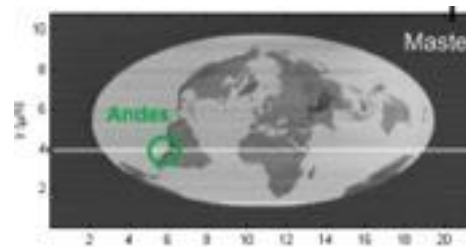
使用NanoFrazor将
3D 图形写入 PPA

电镀镍，
=> 反向主模板

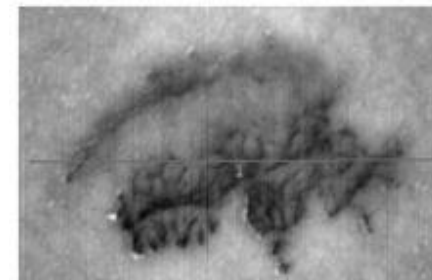
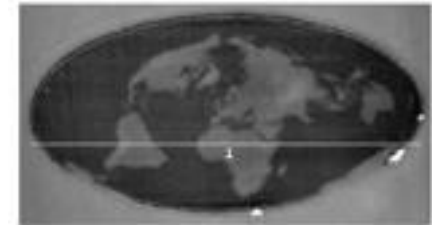
PMMA 注射成型
=> 大量复制



光学显微镜成像



AFM 成像



AFM 成像

SwissLitho AG (Philip Paul)

Applied Microswiss
(Roger Bischofsberger)

FHNW
(Christian Rytka)